

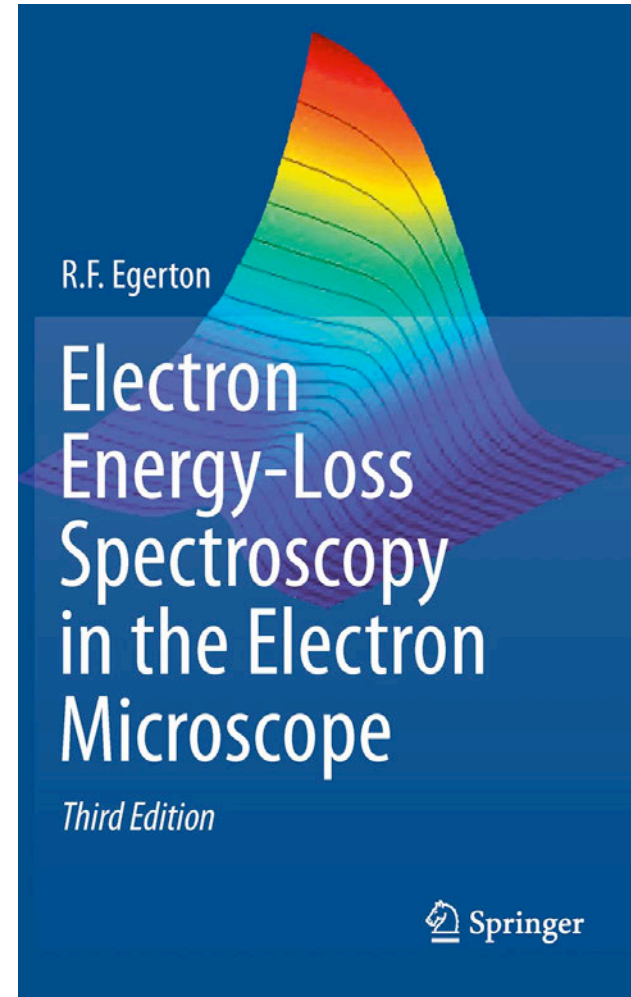
Analytical TEM

part II

Duncan Alexander

EPFL-IPHYS-LSME

- Electron Energy-Loss Spectroscopy in the Electron Microscope
Ray F. Egerton
<https://link.springer.com/book/10.1007/978-1-4419-9583-4>



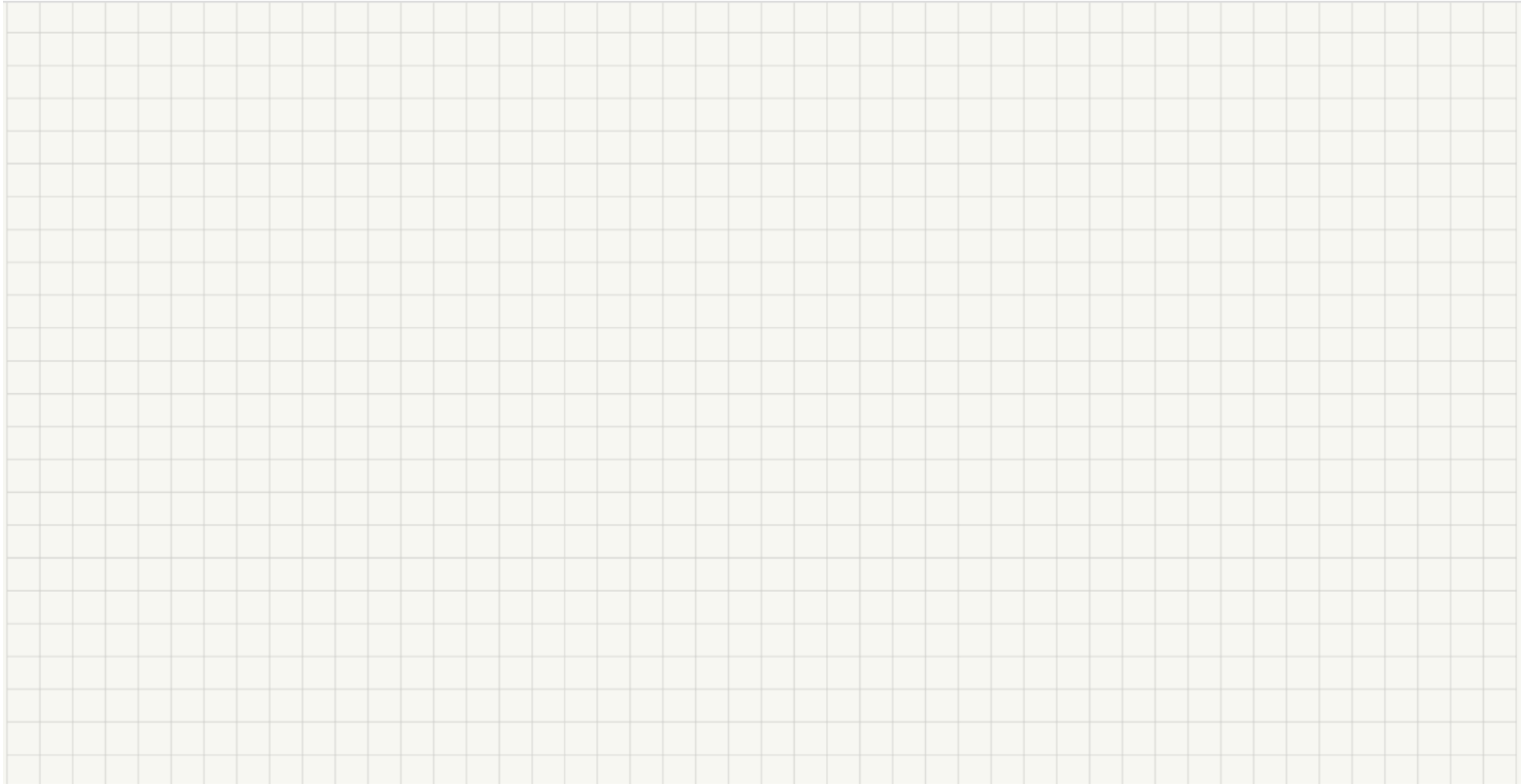
EPFL Contents

- Features of the EEL spectrum
- EELS instrumentation
- Energy-filtered TEM (EFTEM)
- Inelastic scattering geometry
- Low-loss EELS
- Thickness measurements
- Ionisation edge EELS
- Elemental quantification
- ELNES / “fine structure”

EPFL Contents

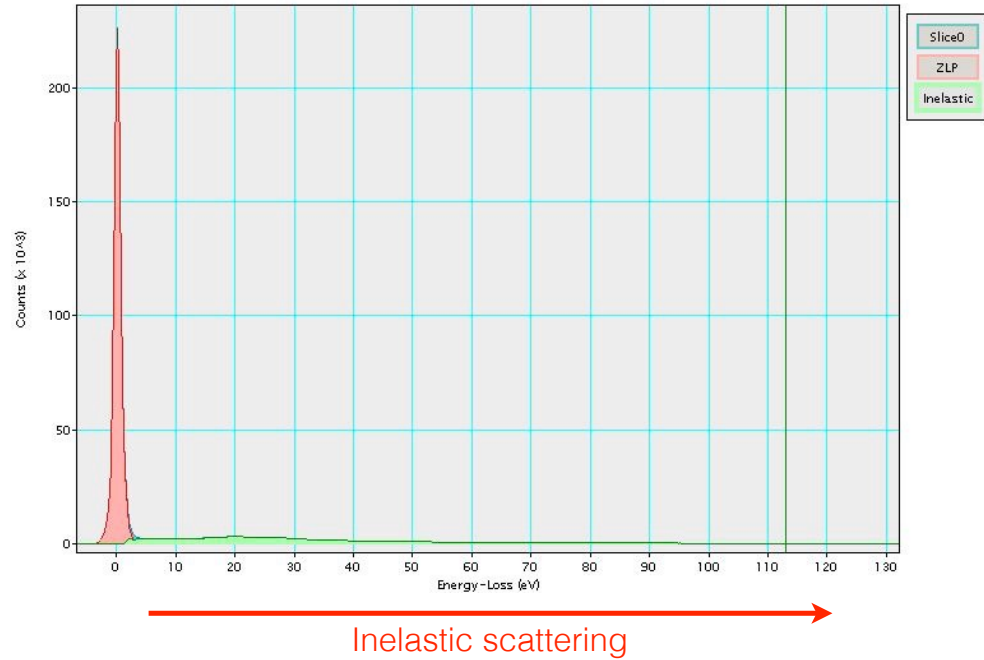
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EPFL Features of the EEL spectrum



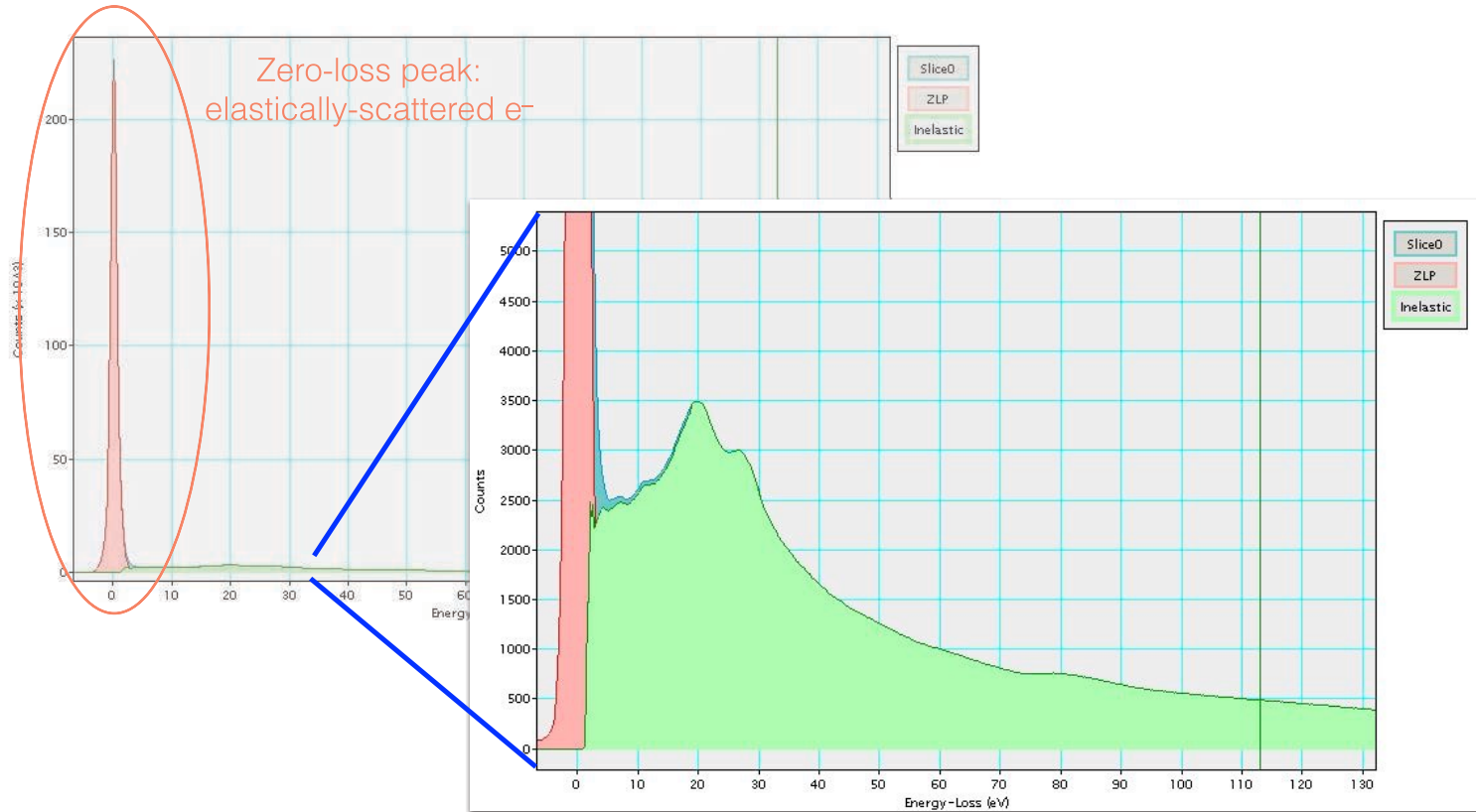
EPFL Features of the EEL spectrum

- Energy loss $> 0 \Rightarrow$ *Inelastic scattering*



EPFL Features of the EEL spectrum

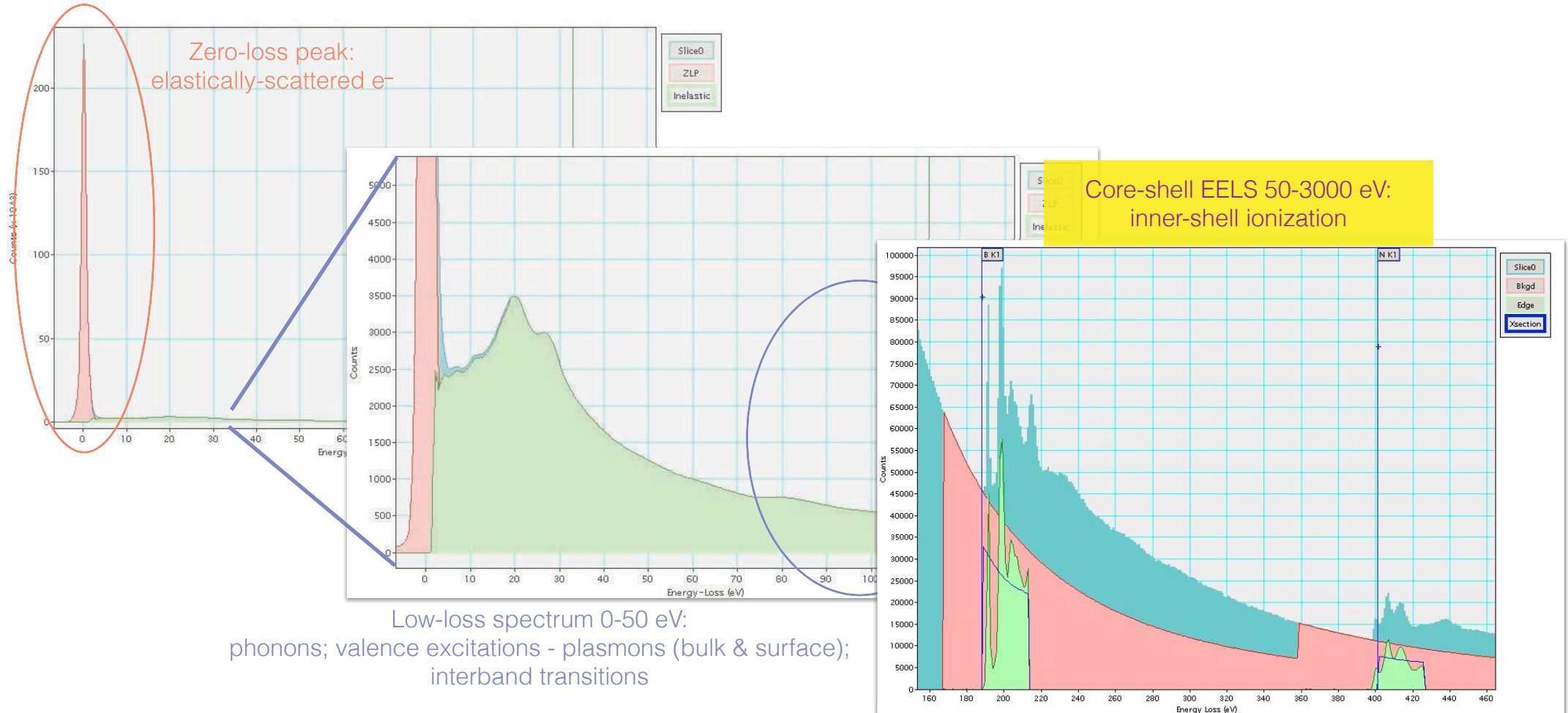
- Energy loss $> 0 \Rightarrow$ *Inelastic scattering*



Low-loss spectrum 0-50 eV:
phonons; valence excitations - plasmons (bulk & surface);
interband transitions

EPFL Features of the EEL spectrum

- Energy loss $> 0 \Rightarrow$ *Inelastic scattering*



EPFL Contents

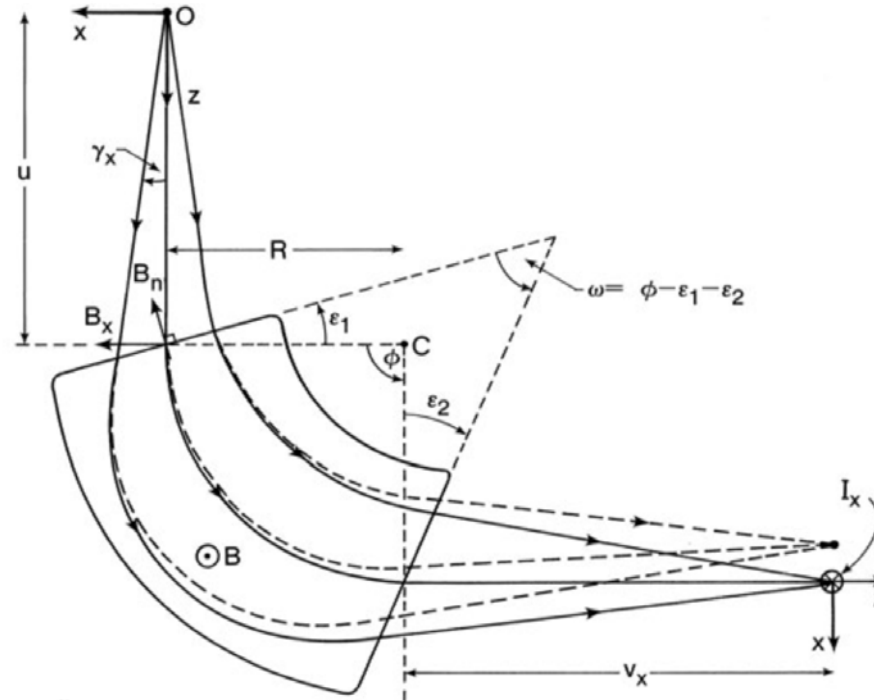
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Electron energy-loss spectrometer

- Typical EEL spectrometer: magnetic prism

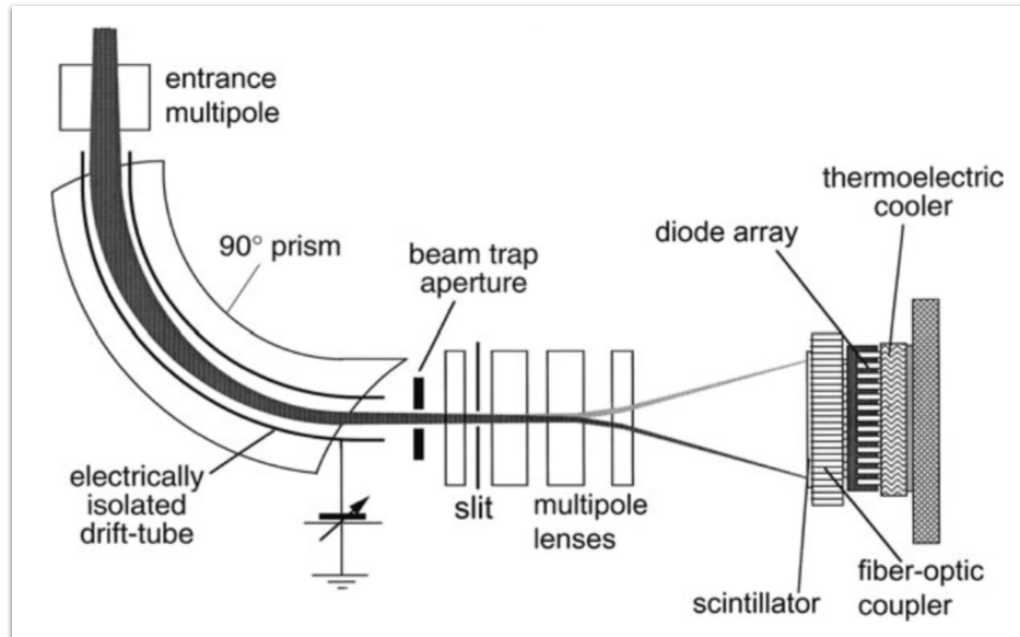
$$R = (\gamma m_0 / eB)v$$

$$\gamma = 1/(1 - v^2/c^2)^{1/2}$$



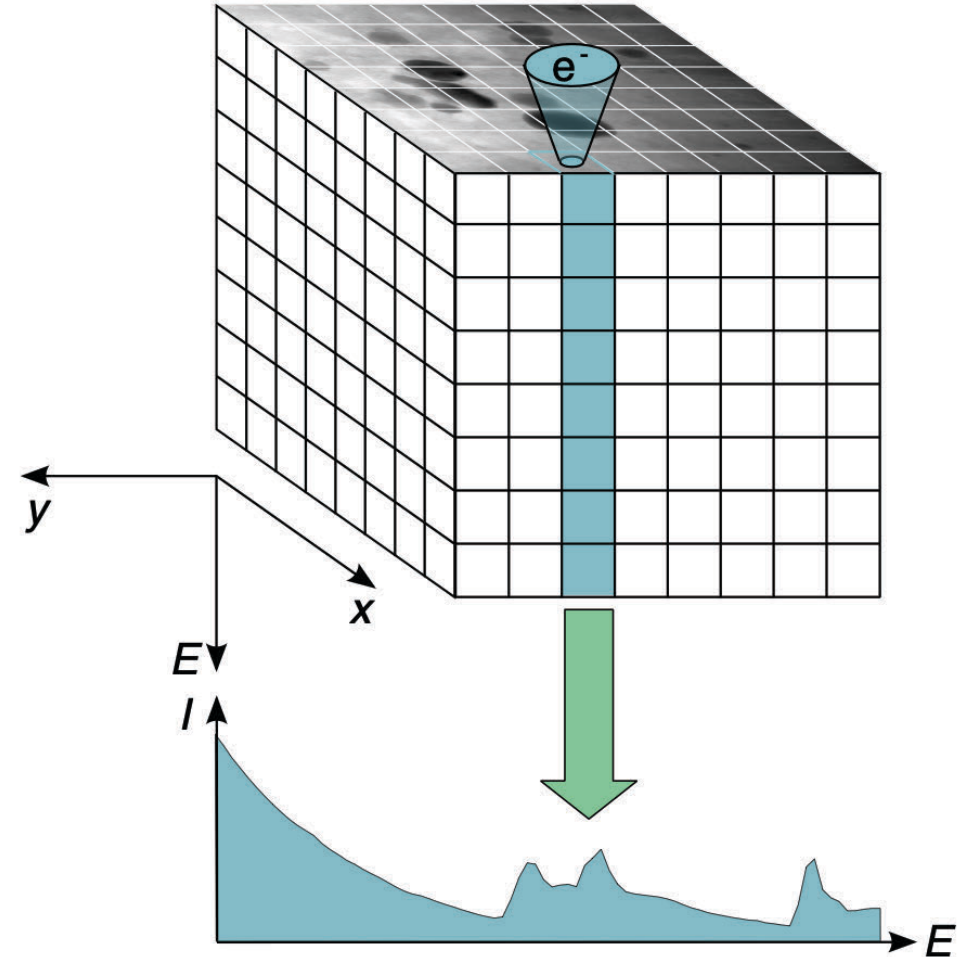
EPFL Post-column spectrometer

- Post-column spectrometer most common type used for materials science/physics
- For instance: Gatan EEL spectrometer



EPFL STEM-EELS spectrum imaging

- During STEM imaging, collect the *forward-scattered* electrons in the spectrometer entrance aperture
- Record 3D data cube with a spectrum for each probe position (x, y)

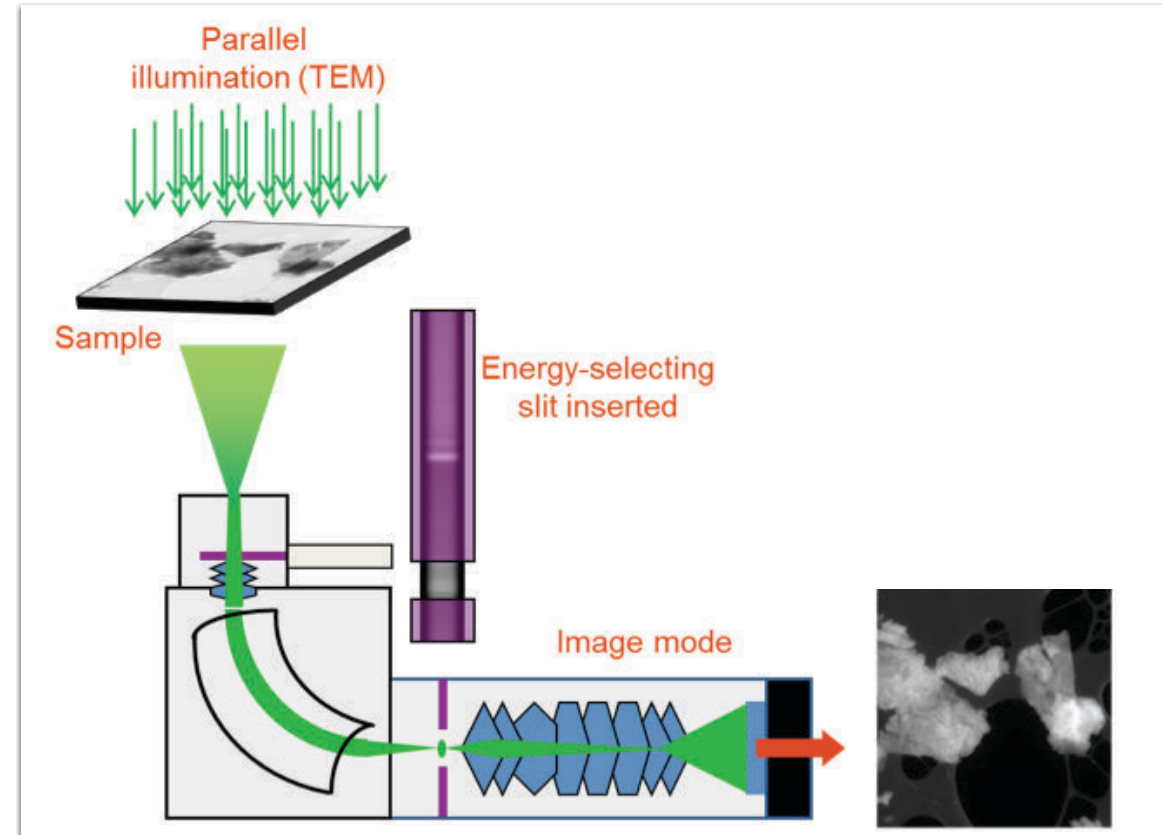


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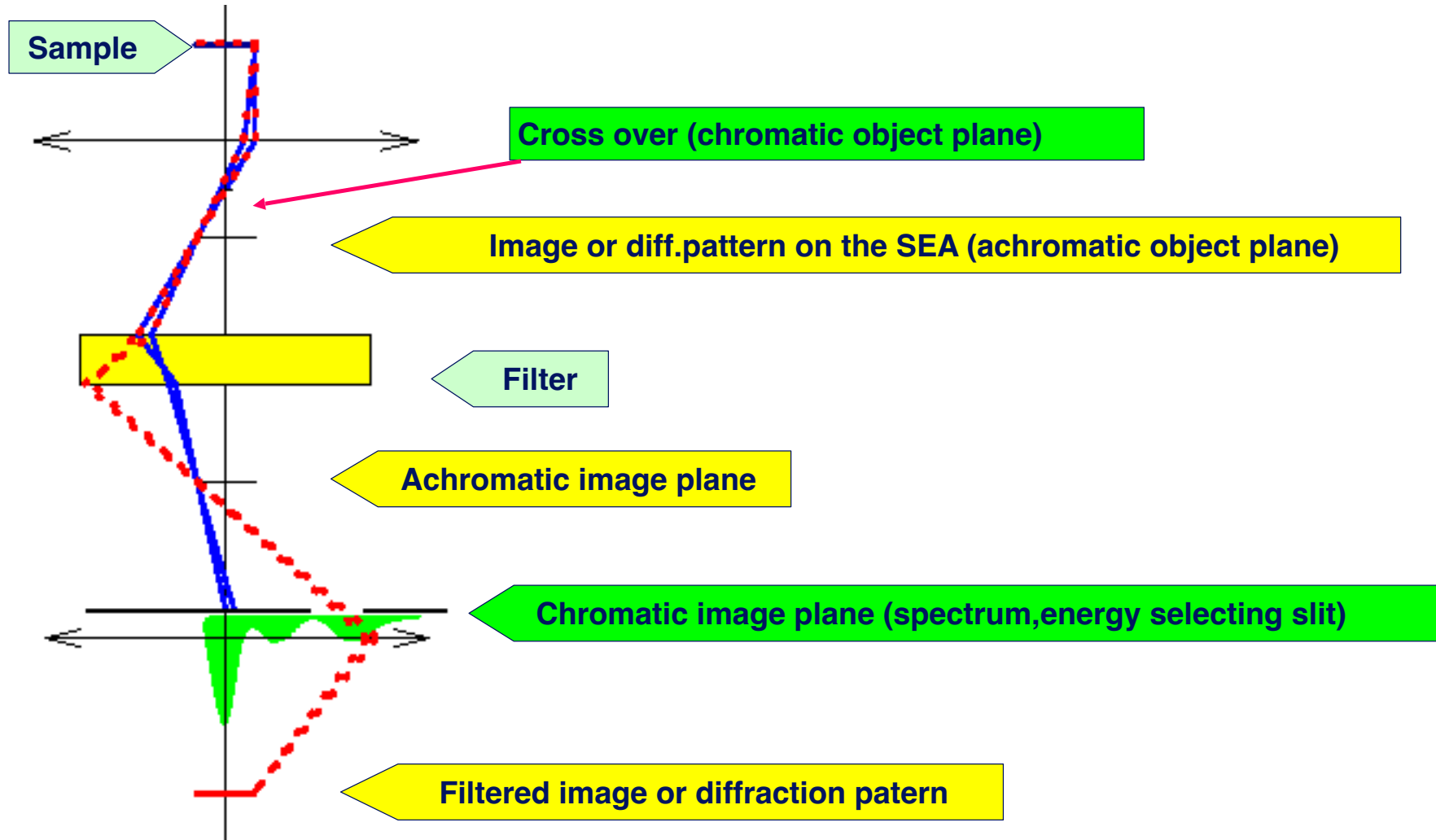
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EPFL Energy-filtered TEM (EFTEM)

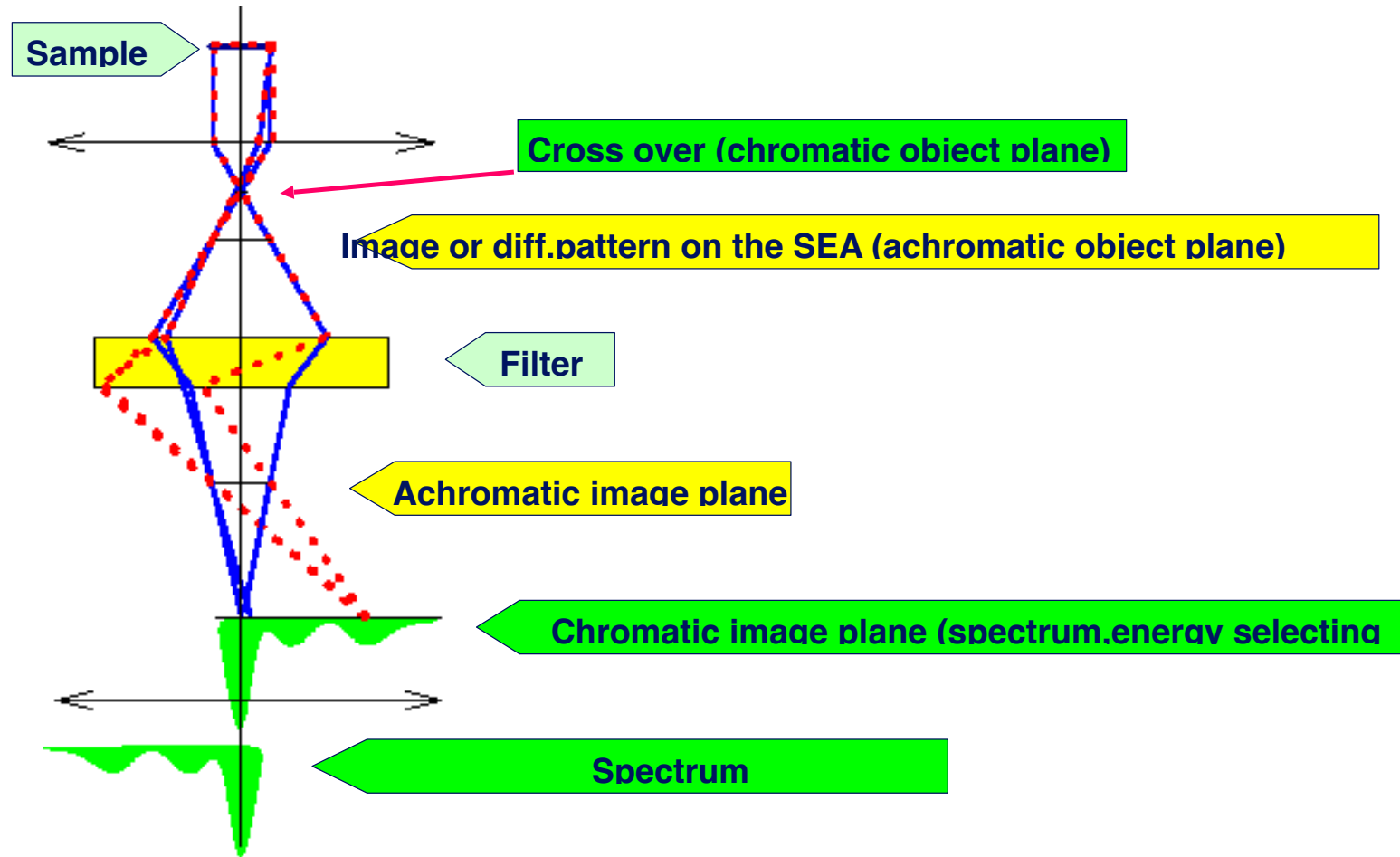
- Record TEM image(s) made from transmitted electrons having certain energy
- Images defined by energy-loss E and energy window
- *Zero-loss* filtering: TEM image of elastically-scattered electrons with no energy loss



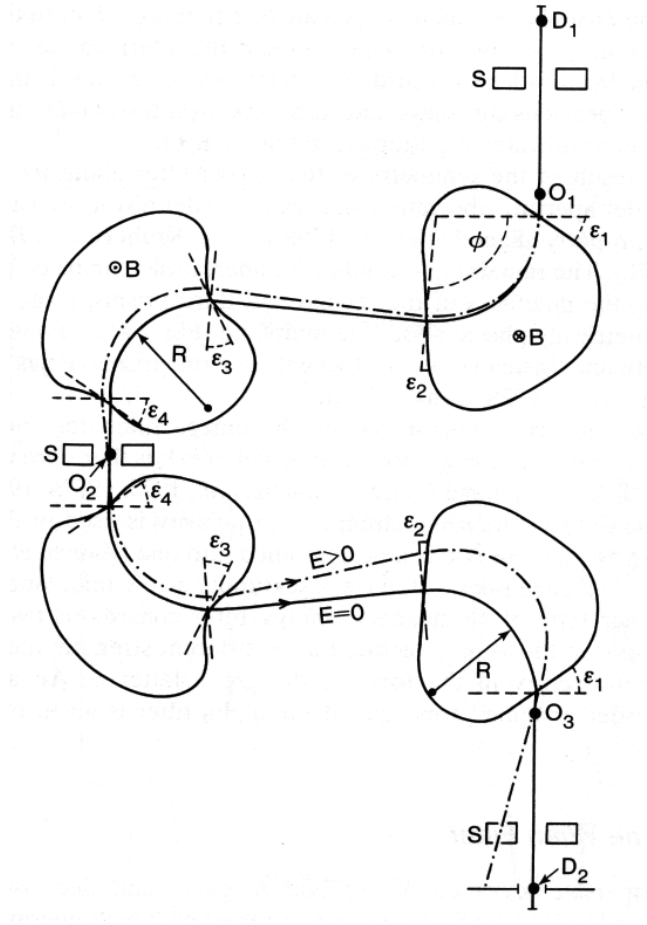
Energy-filtered TEM ray diagram



Spectroscopy mode ray diagram



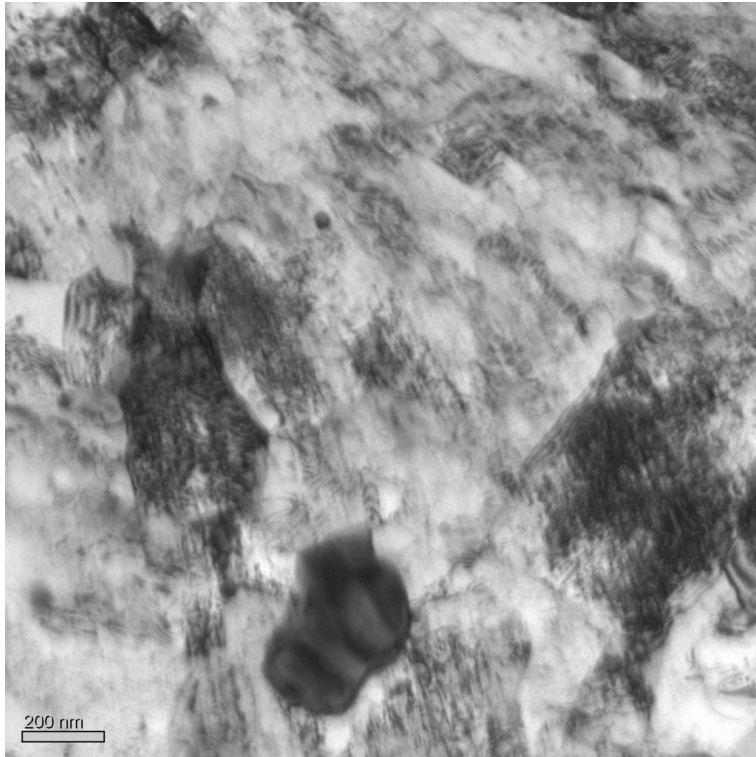
Two possibilities: in-column or post-column



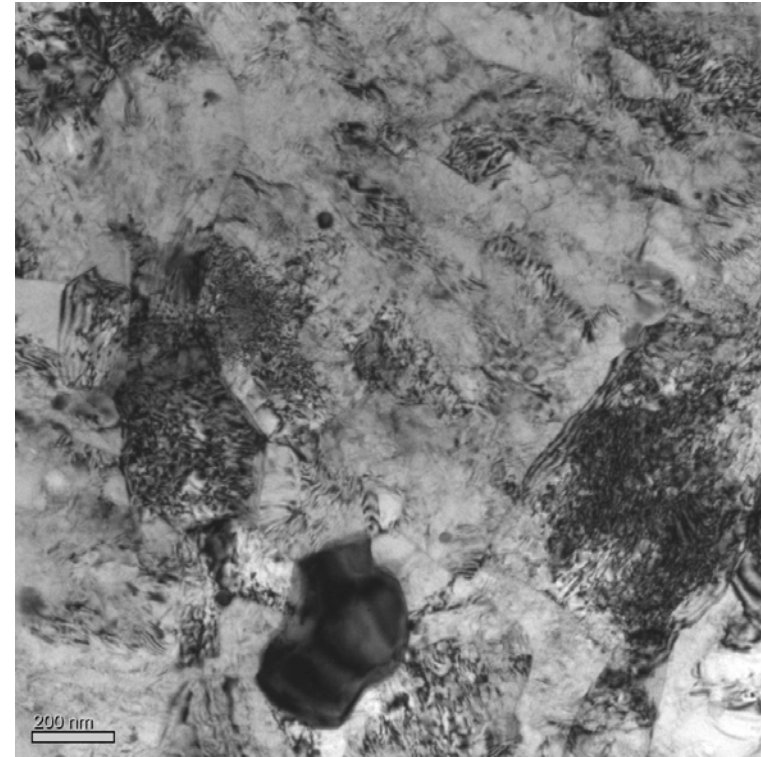
EPFL Zero-loss EFTEM

- Zero-loss filtering can be used to remove diffuse inelastic scattering in TEM images of thick samples and in diffraction patterns
- Example – ODS reinforced steel, sample ~250 nm thick:

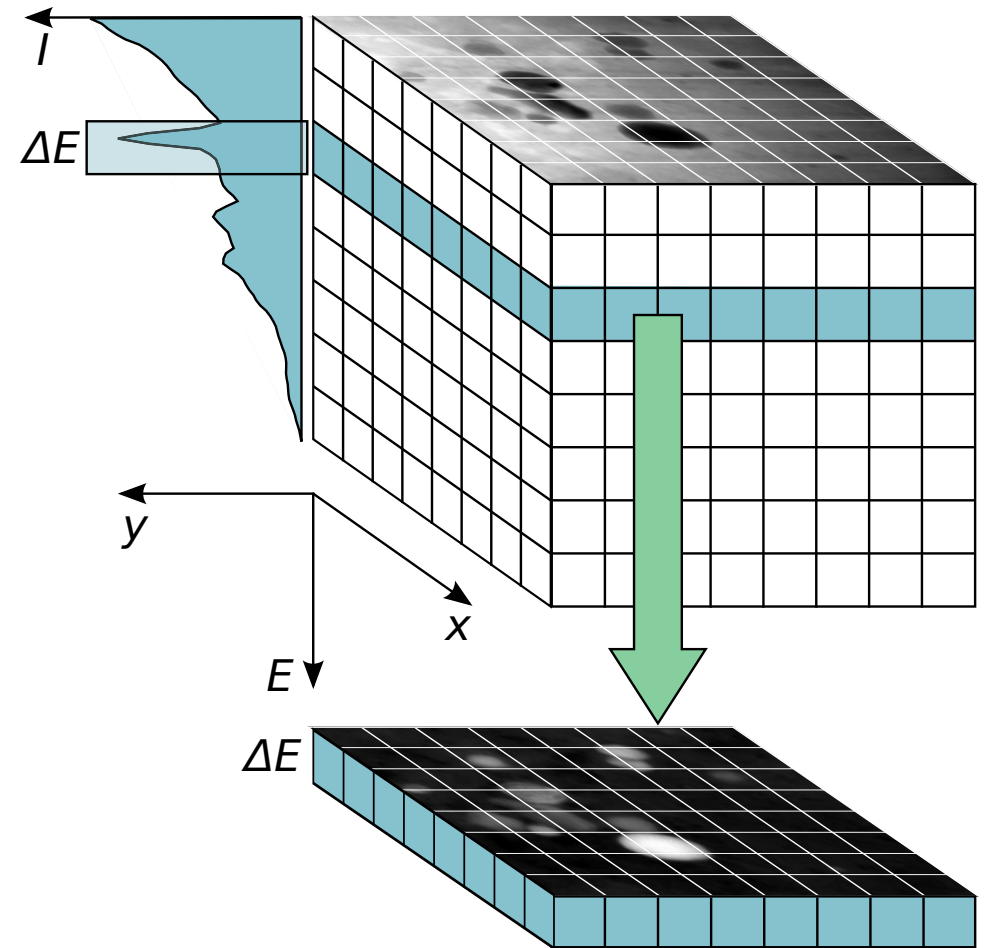
Unfiltered bright-field TEM:



Zero-loss TEM:

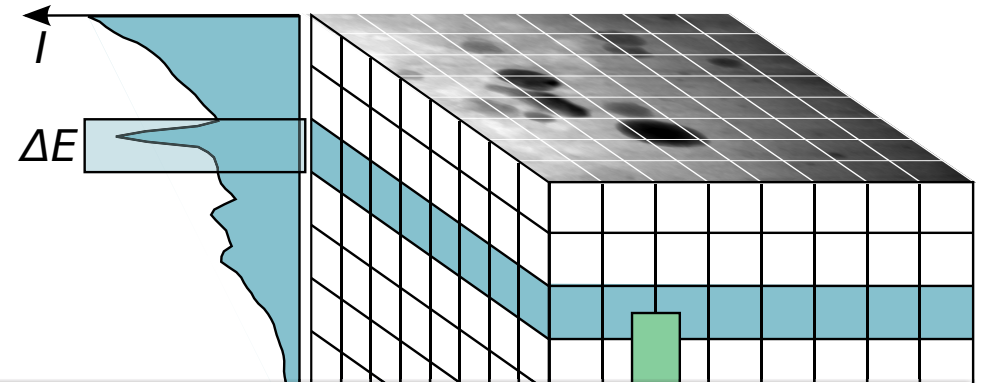


- Record TEM image(s) made from transmitted electrons having a defined energy
- Images defined by energy-loss E and energy window ΔE
- *Zero-loss* filtering: TEM image of elastically-scattered electrons with no energy loss
- EFTEM spectrum imaging: create 3D data-cube by recording image series at consecutive energy losses



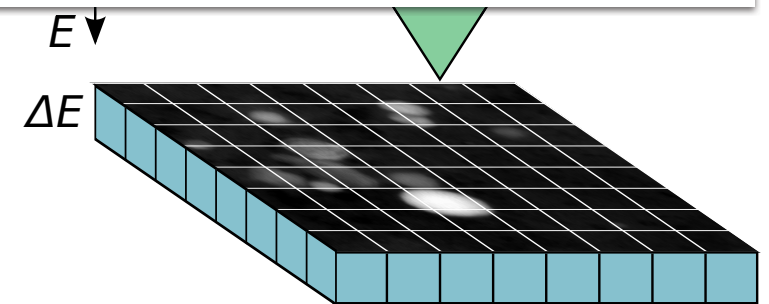
EPFL Energy-filtered TEM (EFTEM)

- Record TEM image(s) made from transmitted electrons having a defined energy
- Images defined by energy-loss E and energy window ΔE



No equivalent with EDXS!
EDXS mapping can only be done in STEM mode

- EFTEM spectrum imaging: create 3D data-cube by recording image series at consecutive energy losses



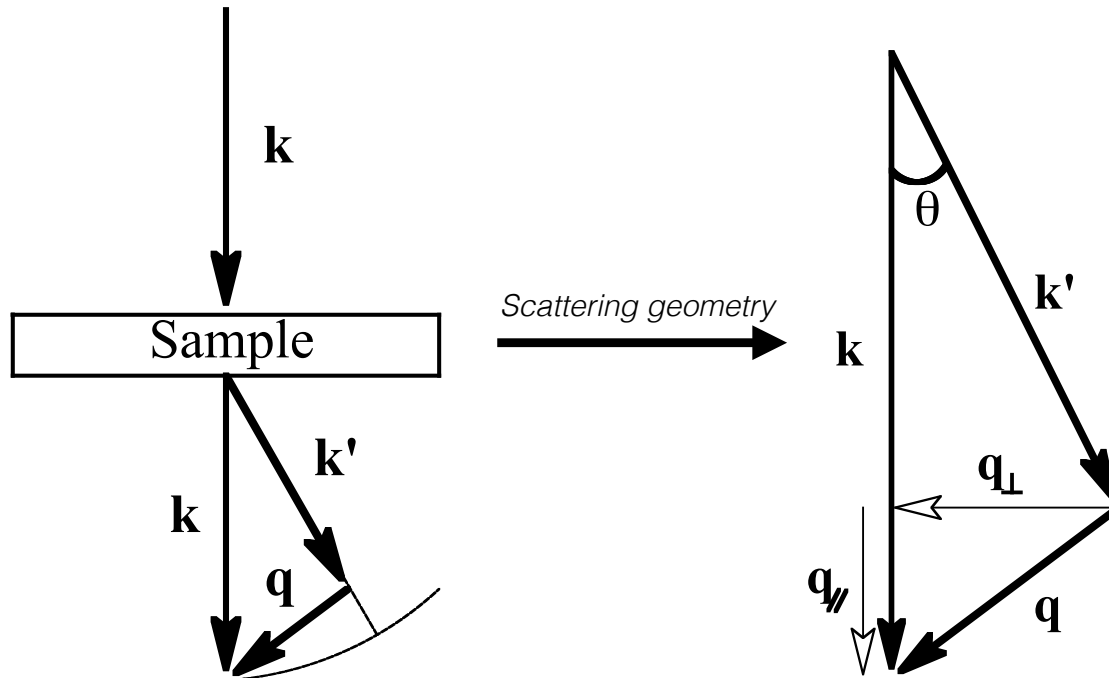
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EPFL Inelastic scattering geometry

\vec{k} – incident wave-vector
 \vec{k}' – scattered wave-vector

$$q^2 = k^2 + (k')^2 - 2 k k' \cos \theta$$



$$\theta_E = \frac{Em\gamma}{\hbar^2 k^2}$$

$$q_{\perp} = k\vartheta \text{ (geometry)}$$

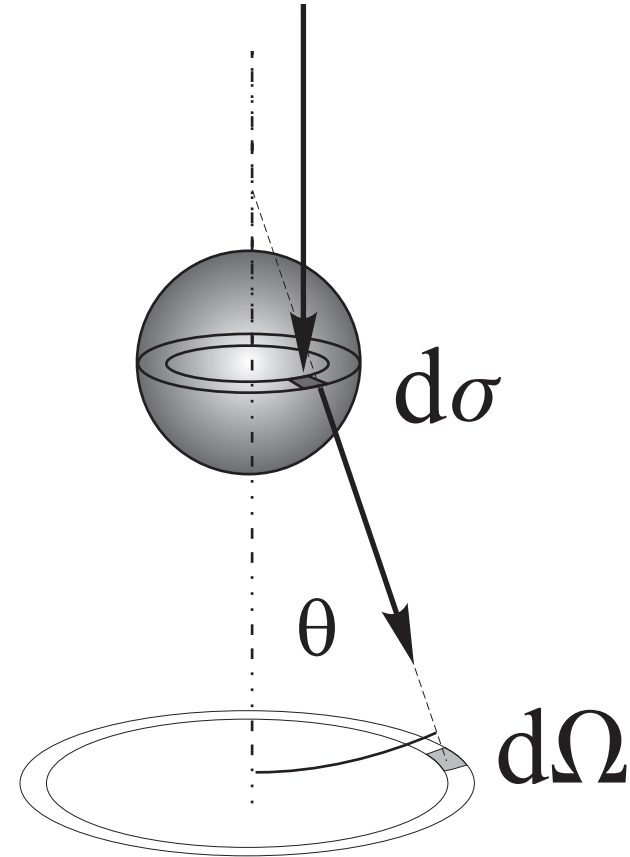
$$q_{\parallel} = k\vartheta_E \text{ (definition of } \vartheta_E)$$

$$\vartheta \ll 1 \text{ therefore } q^2 = k^2(\vartheta_E^2 + \vartheta^2)$$

Relevant quantity: the *double differential scattering cross-section* (DDSCS) as a function of angle θ and energy loss E .

It is given for one atom.

We consider a transition from initial state $|I\rangle$ to final state $|F\rangle$ for the core electron of the atom



EPFL Angular distribution of the ionisation edge

With quantum mechanical derivation, find that DDSCS for inelastic events varies as $\frac{1}{q^2}$

$$\text{Since: } q^2 = k^2(\theta^2 + \theta_E^2)$$

$$\text{DDSCS has an angular dependence: } \text{DDSCS}(\theta) \propto \frac{1}{\theta^2 + \theta_E^2}$$

Therefore the ionisation edge has an angular distribution of intensity that is **Lorentzian**

$$\frac{\partial^2 \sigma}{\partial \Omega \partial E} \propto \frac{1}{\theta^2 + \theta_E^2}$$

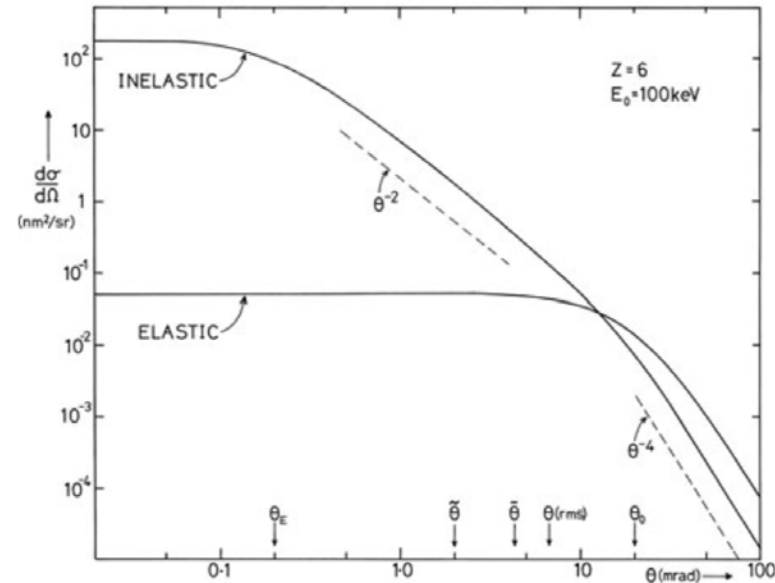
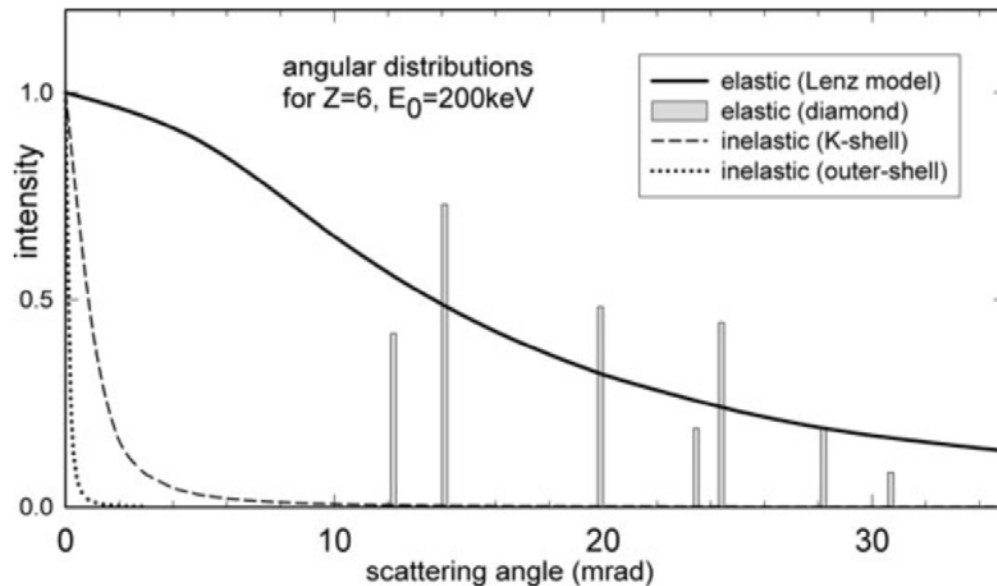
θ_E is the scattering angle for the half width at half maximum (HWHM) of this Lorentzian

θ_E is therefore considered as the *characteristic angle of scattering*, because most of the ionisation edge intensity will fall within a collection aperture of this angle

EPFL Inelastic scattering angular range

- Inelastic scattering concentrated into much smaller angles than elastic scattering

- Characteristic angle for scattering:
$$\theta_E = \frac{Em\gamma}{\hbar^2 k^2} = \frac{E}{\gamma m v^2} \sim \frac{E}{2E_0}$$



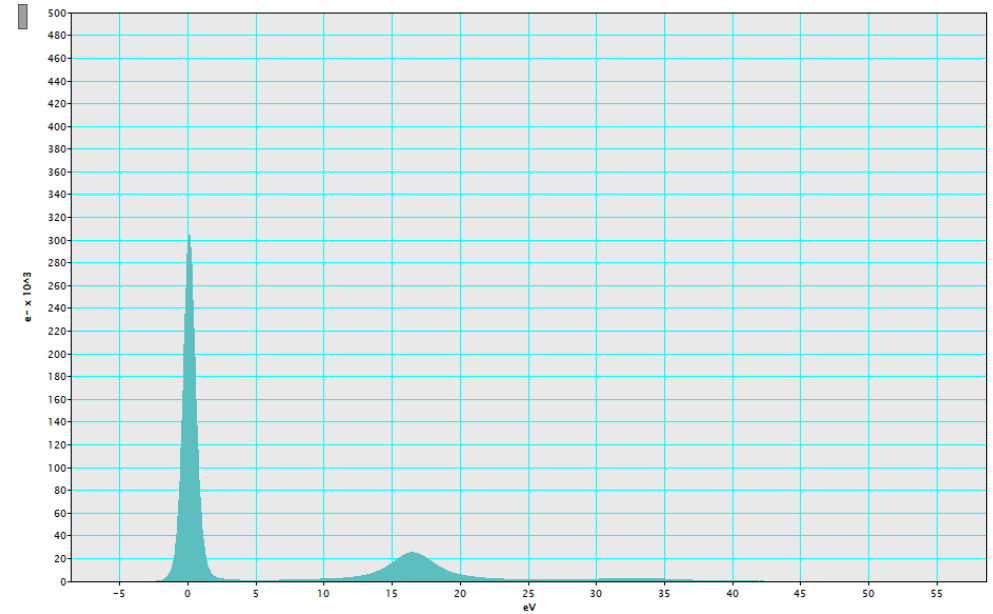
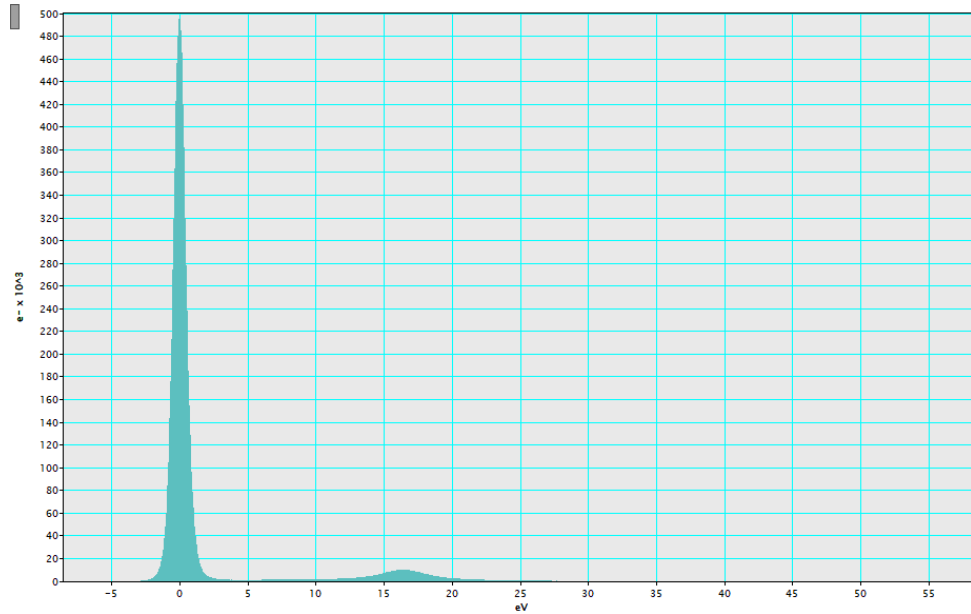
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EPFL Low-loss EELS

- For $\Delta E \sim 1\text{--}50$ eV: excitation of plasmons
- Volume/bulk plasmon: oscillation of valence electrons

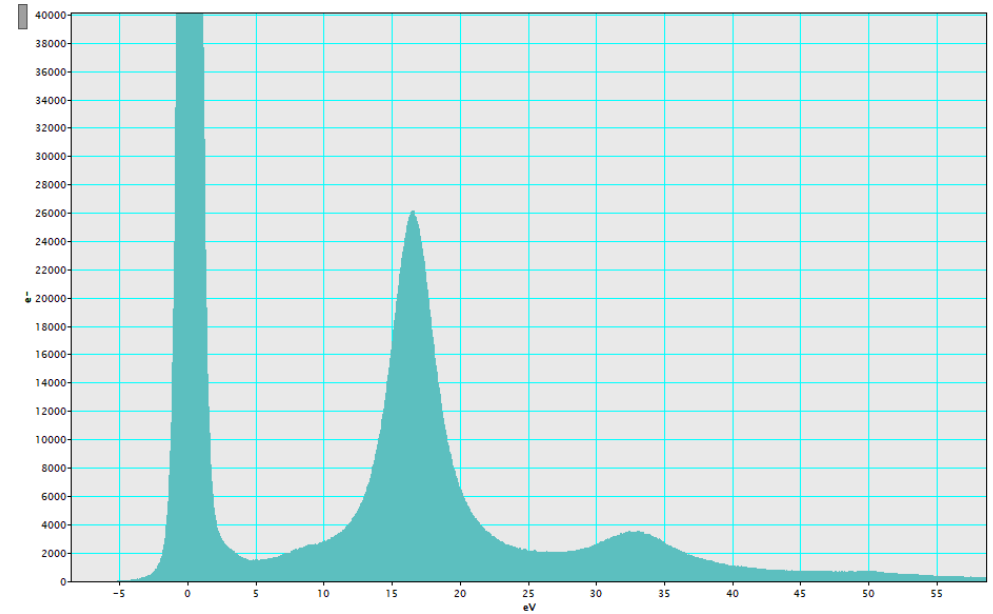
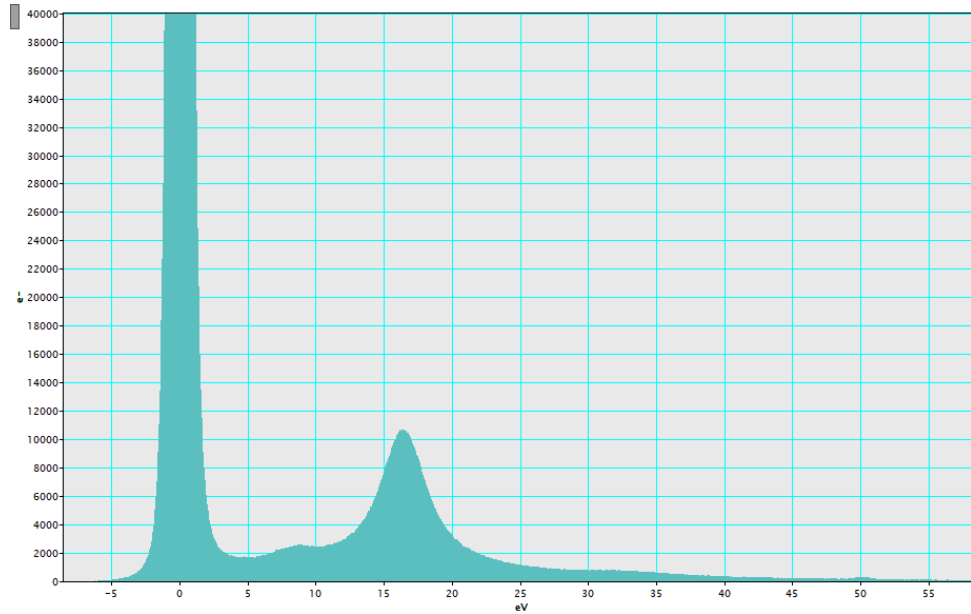
Example low-loss: crystalline Si



EPFL Low-loss EELS

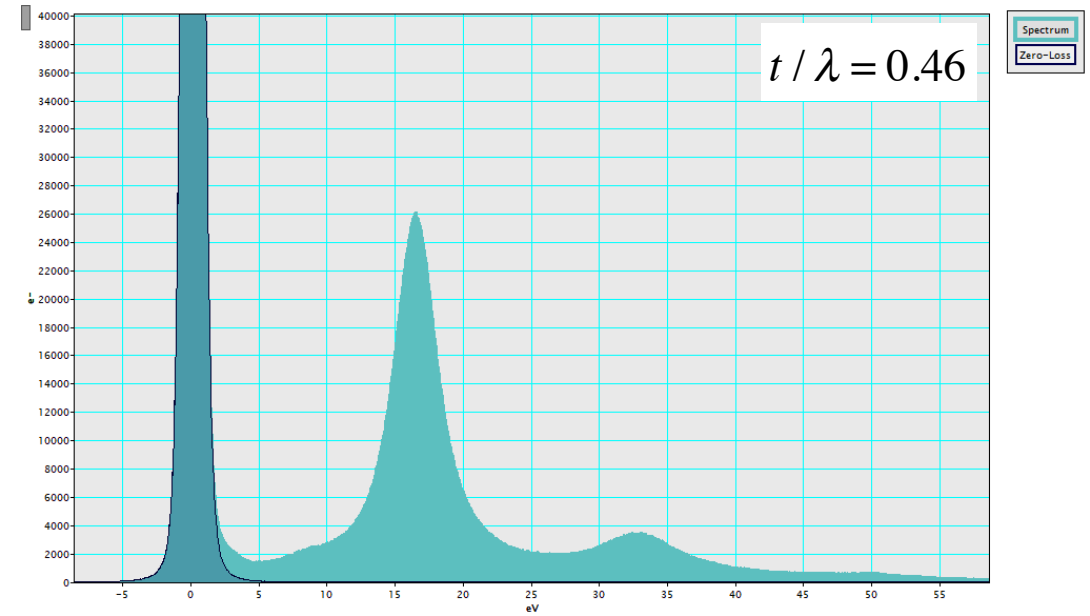
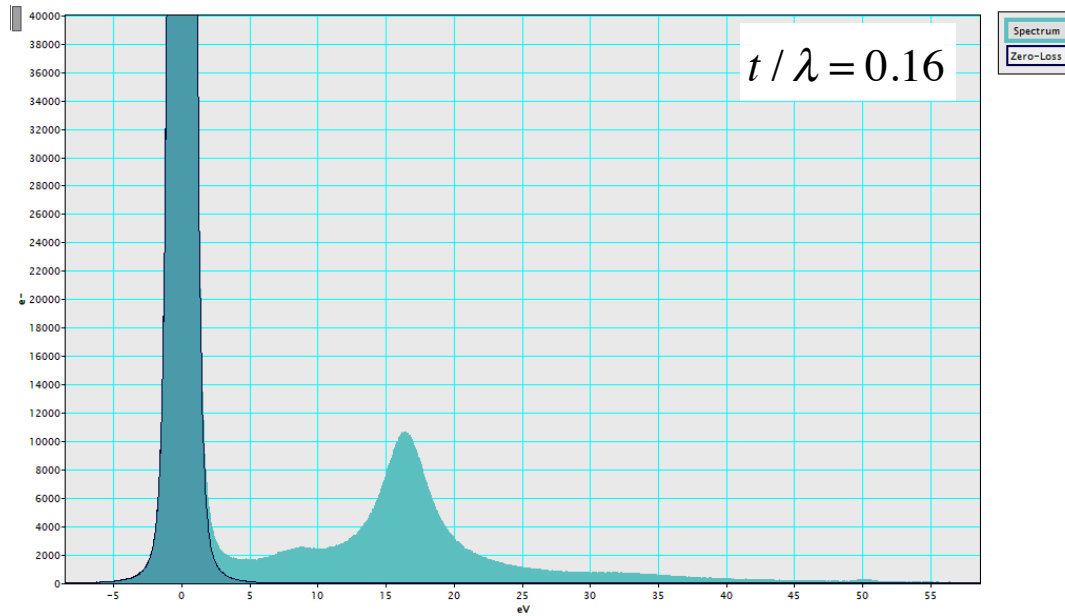
- For $\Delta E \sim 1\text{--}50$ eV: excitation of plasmons
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Example low-loss: crystalline Si



EPFL Plural scattering

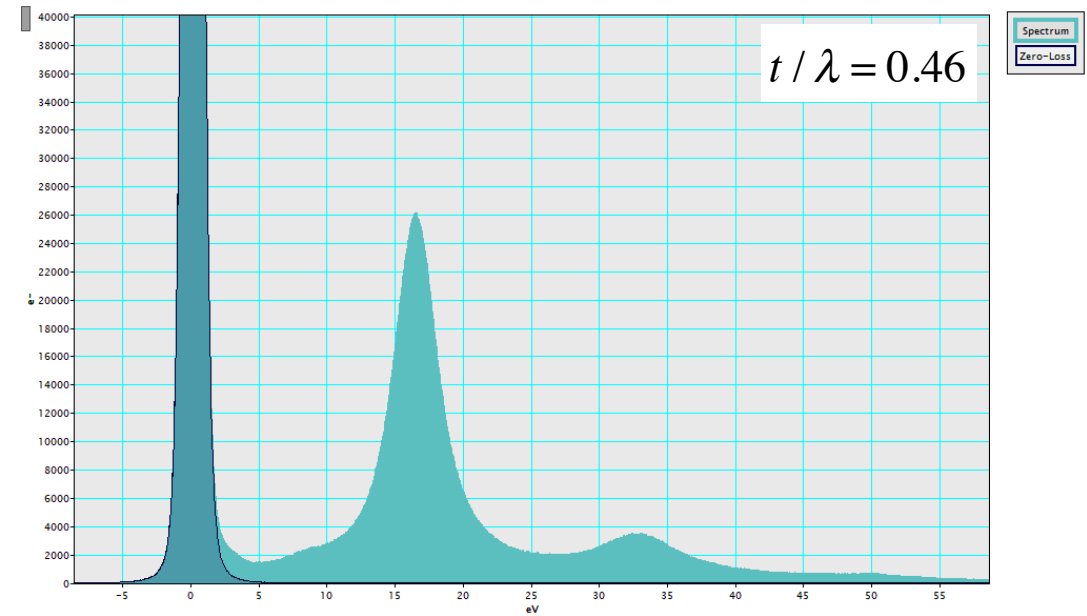
- As specimen thickness increases, can have multiple scattering: *plural scattering*
- **Inelastic scattering mean free path: λ**
- From Poisson statistics: $t/\lambda = \ln(I_t/I_0)$



EPFL Plural scattering; mean free path

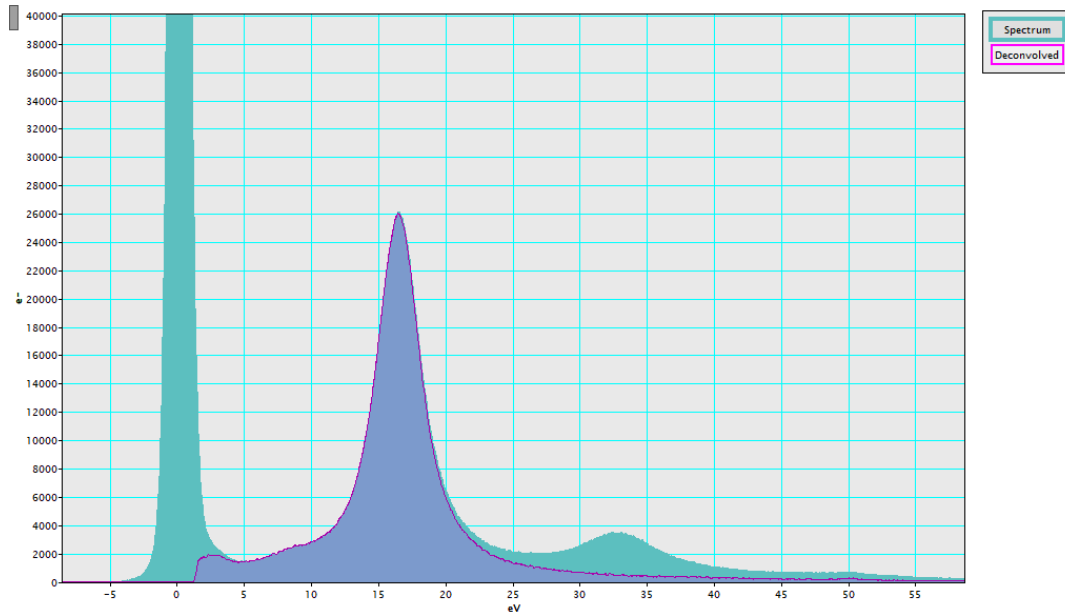
- What is likely to influence the inelastic scattering mean free path?

- By calculating λ the sample thickness t can be estimated
- Two routines in Digital Micrograph:
 - Kramers-Kronig sum rule
 - Log-ratio (absolute) – Bethe sum rule
- Accuracy $\sim \pm 5\text{--}10\text{ nm}$



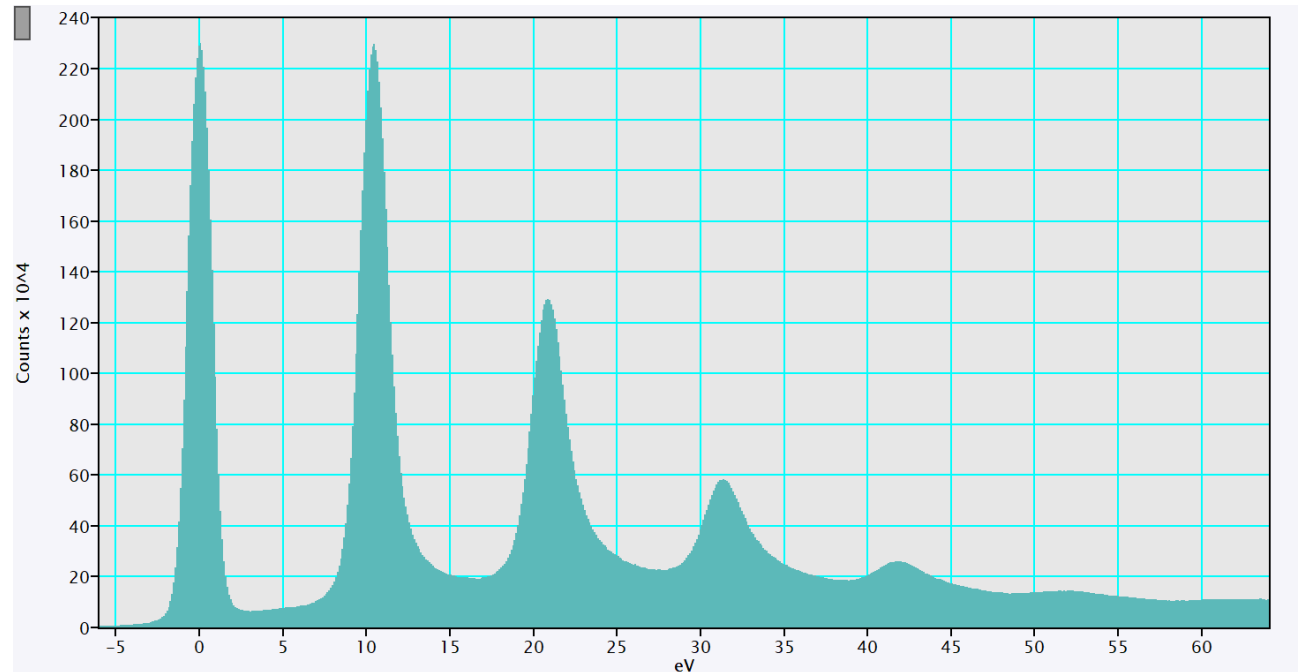
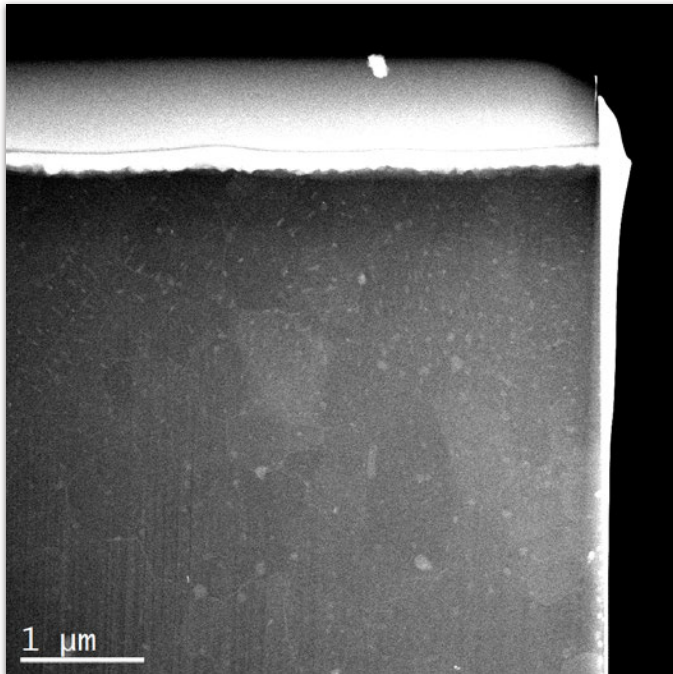
EPFL Spectral deconvolution

- Deconvolution can be used to retrieve the *single-scattering distribution* (SSD)
- Core-loss spectra: use Fourier-ratio deconvolution (needs low-loss spectrum)
- Low-loss spectra: use Fourier-log deconvolution:



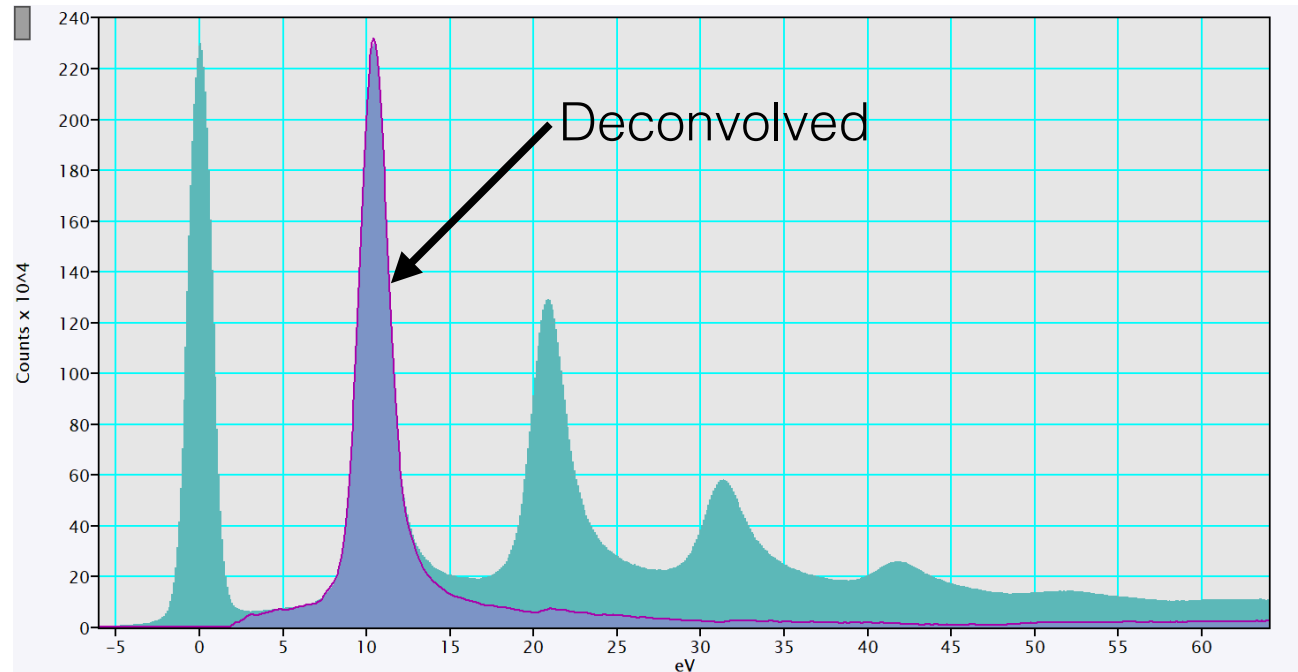
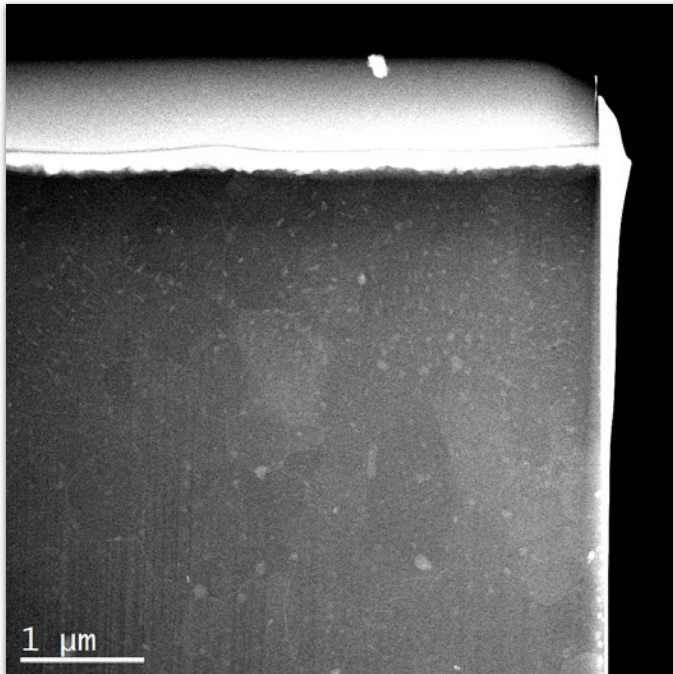
EPFL Multiple scattering: Mg sample

- Thick sample: $t / \lambda \approx 2.3$
- Well-defined plasmon peak (free electron gas)
- Multiple orders of plasmon peak excitation



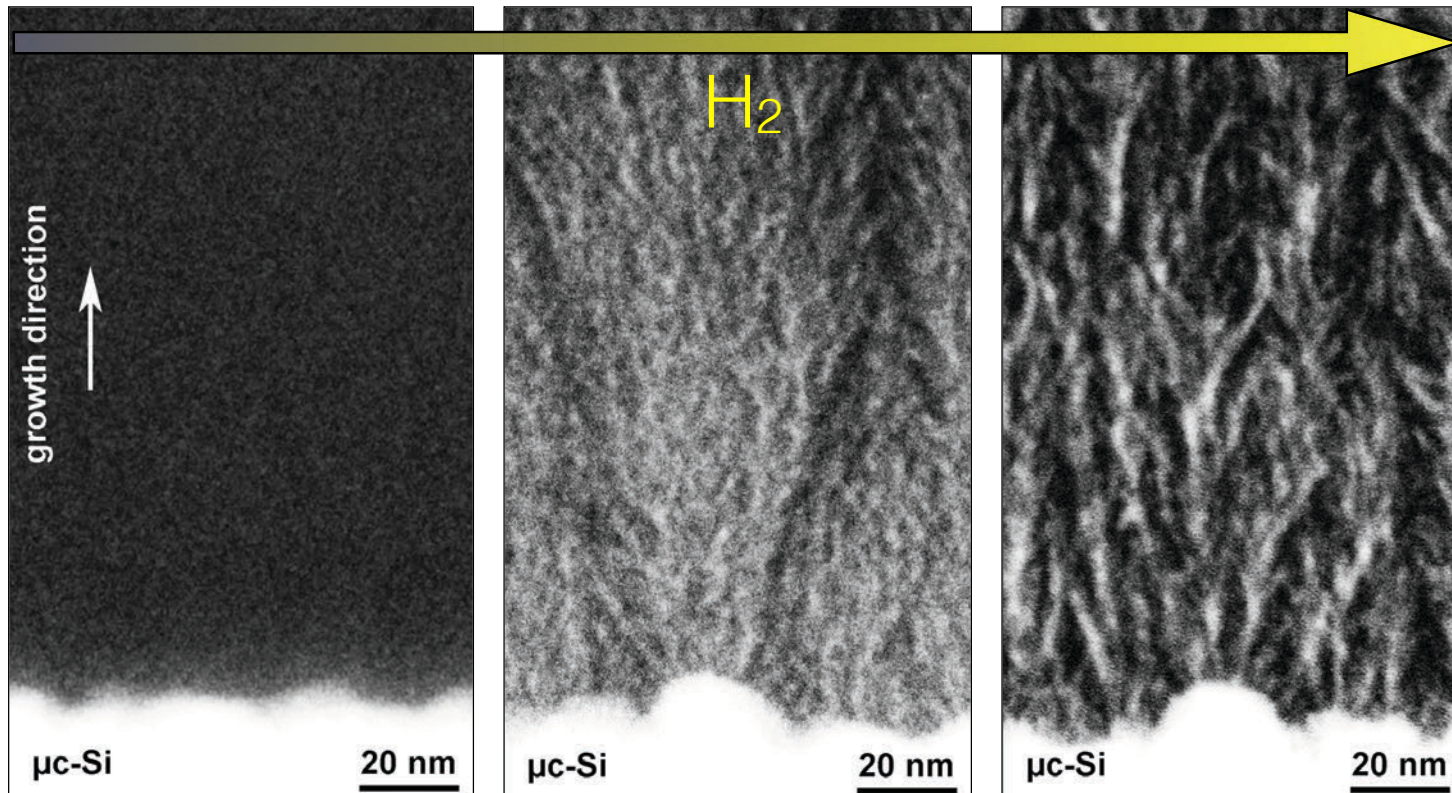
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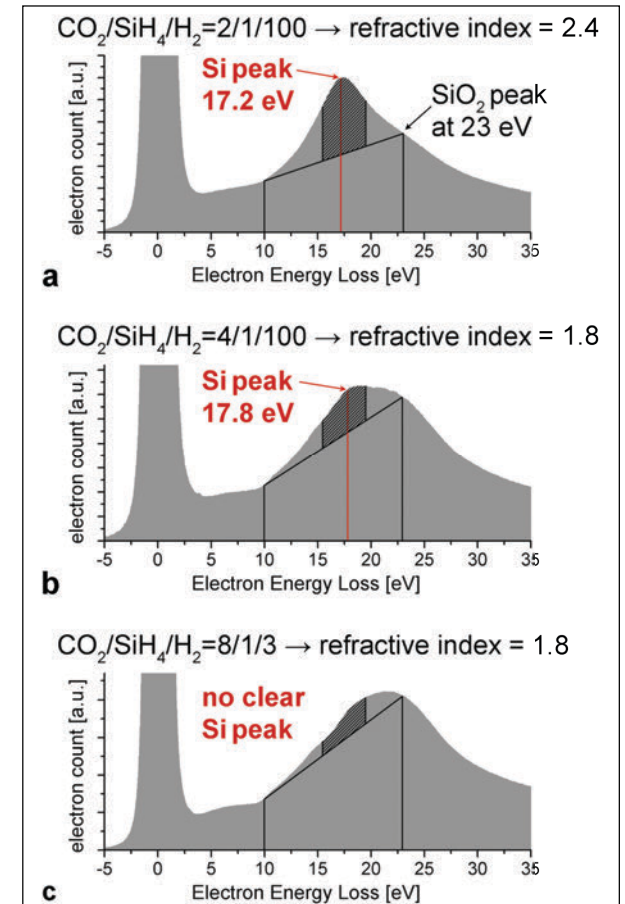


EPFL Ex. plasmon use: mapping elemental Si

- Use plasmon peak to map elemental Si nano-filaments in SiO_x thin films



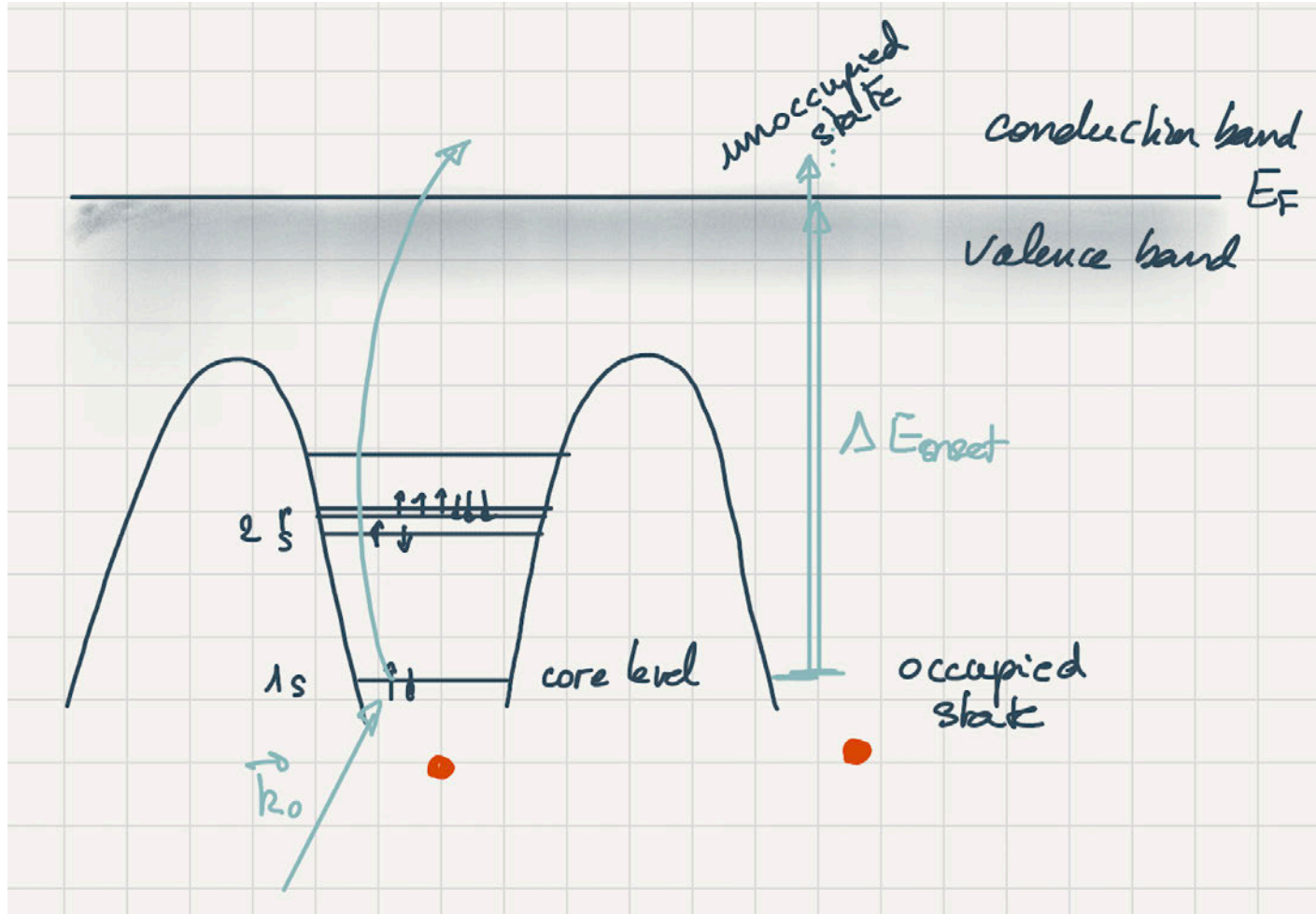
- Increasing H_2 plasma \Rightarrow increased phase separation



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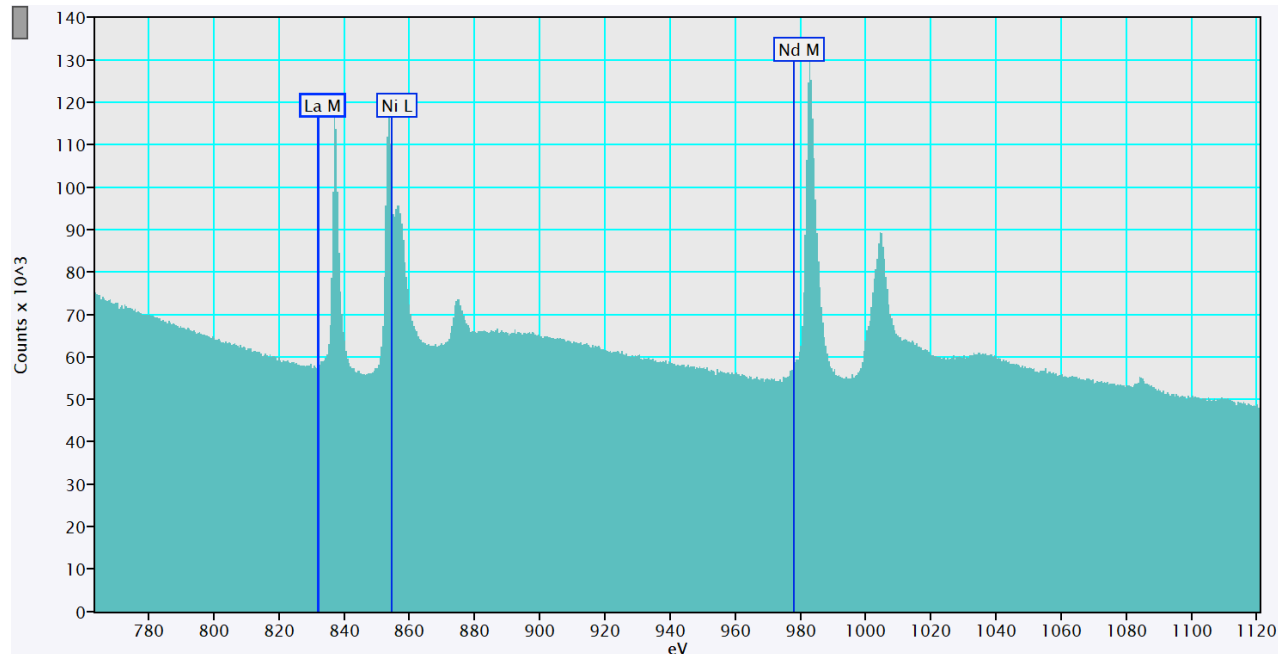
EPFL Ionisation edge / “core-loss” EELS



EPFL Ionisation edge / “core-loss” analysis

- Elemental ionisation edges superimposed on exponentially decaying background (fit with power-law model)
- Signal intensity proportional to projected atomic concentration and elemental partial ionisation scattering cross-section $\Delta\sigma$

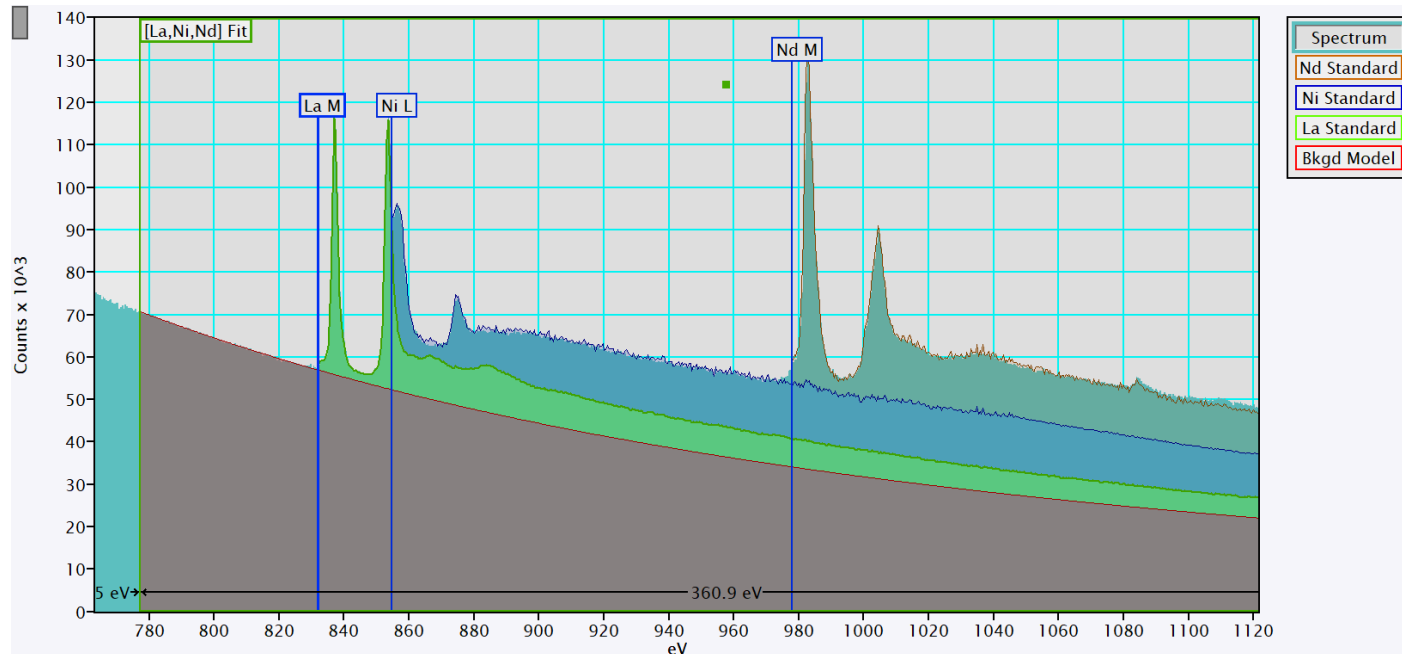
(La, Nd)NiO₃ alloy



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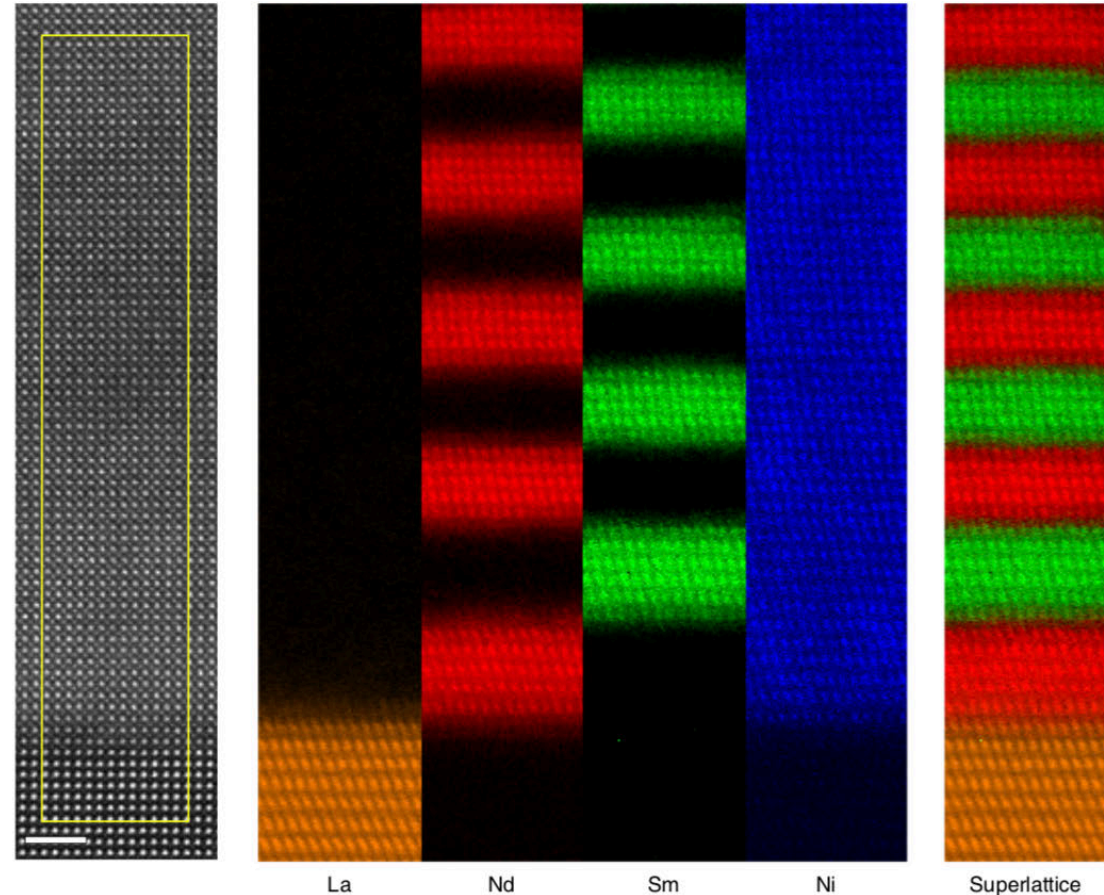
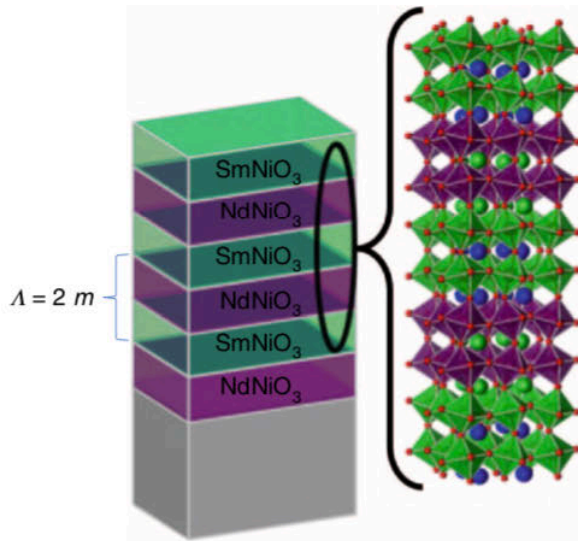
(La, Nd)NiO₃ alloy



EPFL Elemental mapping – STEM-EELS

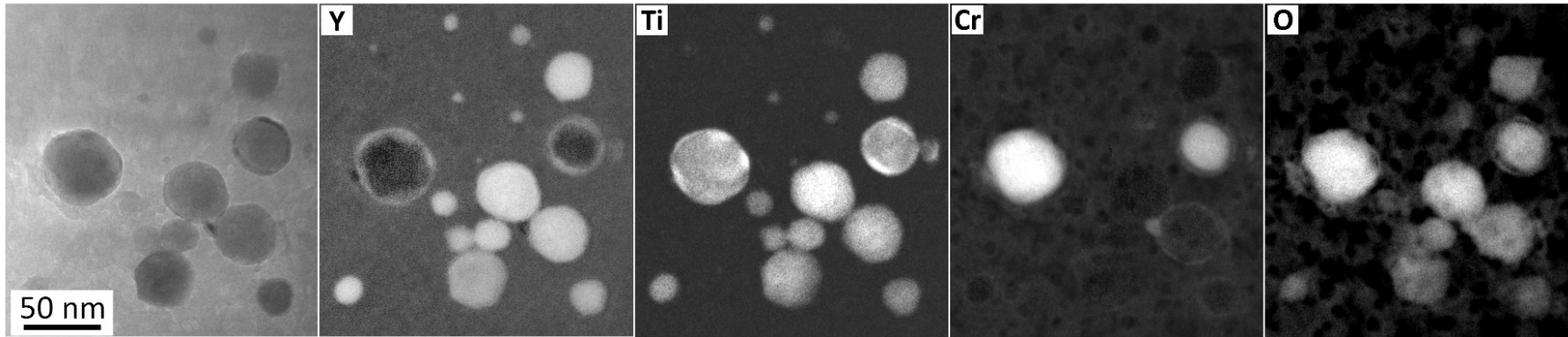
- Produce elemental maps by plotting integrated intensity in background-subtracted energy-loss “windows” that select different ionisation edges

Example: NdNiO_3 / SmNiO_3 superlattice on LaAlO_3

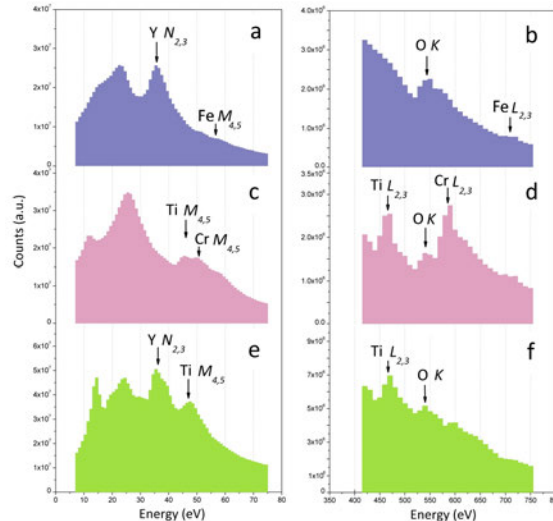


EPFL Elemental mapping – EFTEM

- Example: EFTEM spectrum imaging of ODS reinforced steel
- Statistics obtained on spatial distribution of different particle types



Spectral fingerprints:



← Y-O particles: 6%, 16 nm

← Ti-Cr-O particles: 4%, 33 nm

← Y-Ti-O particles: 90%, 6 nm

EPFL Partial scattering cross section

The **partial cross section** for ionization of shell n is

$$\Delta\sigma = \int_{E_n}^{E_n + \Delta E} \int_{\Delta\Omega} dE d\Omega \frac{\partial^2 \sigma}{\partial E \partial \Omega}. \quad (1)$$

$\Delta\sigma$ has dimension m^2/atom .

An incident beam *current density* j_0 causes, in a specimen with number of atoms N irradiated by the beam, within $\Delta E \Delta\Omega$ a probe current

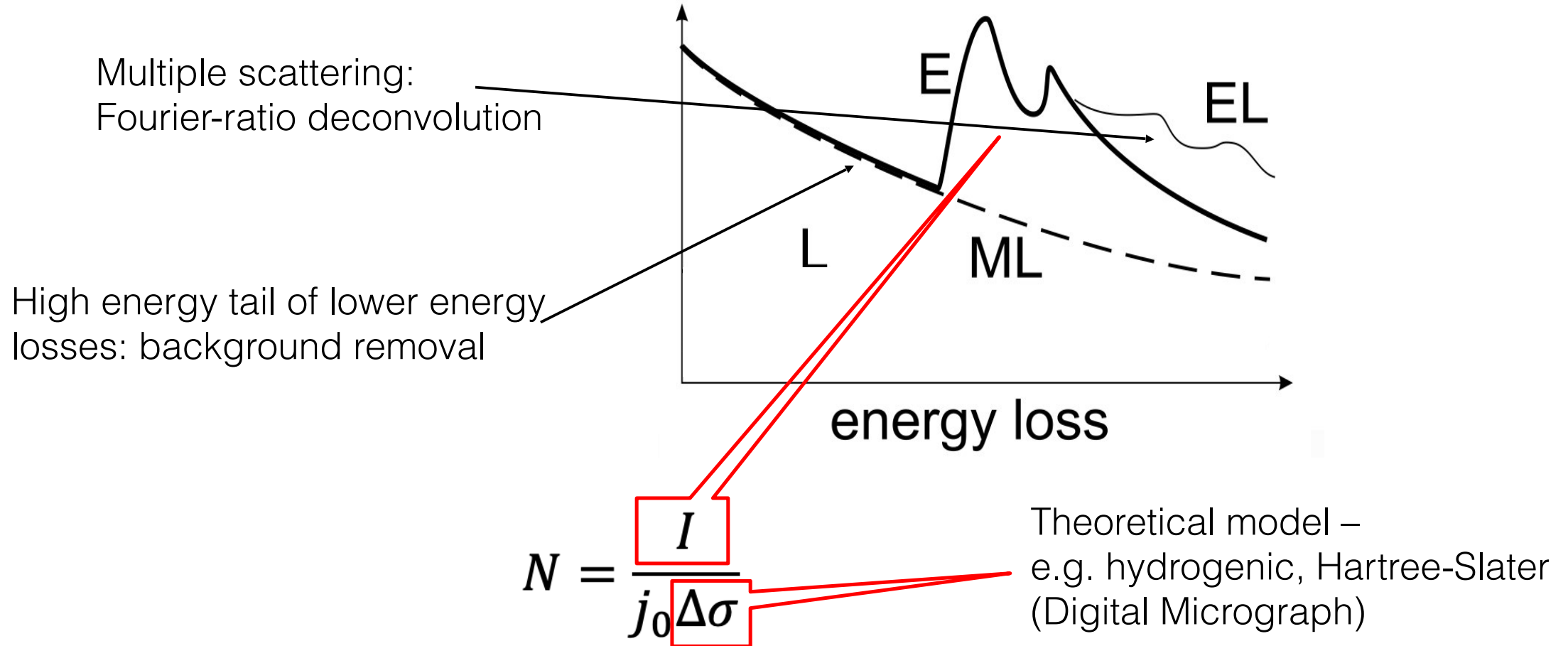
$$I = N \Delta\sigma j_0. \quad (2)$$

Here, we have ignored the background signal, as well as multiple scattering.

The number N of atoms irradiated by the probe is then

$$N = \frac{I}{j_0 \Delta\sigma}. \quad (3)$$

EPFL Ionisation edge / “core-loss” analysis



EPFL Elemental quantification

- Number of atoms per unit area N given by:
$$N = \frac{I}{j_0 \Delta \sigma}$$
- Elemental percentages calculated using:
$$\frac{N_a}{N_b} = \frac{I_a}{I_b} \frac{\Delta \sigma_b}{\Delta \sigma_a}$$
- For good quantification, need knowledge and correct choice of convergence semi-angle α and EEL spectrometer collection semi-angle β
- Fit background with power-law model: $I_B = AE^{-r}$

EPFL Elemental quantification

- Example: BN measured in TEM mode at 200 keV:
- B K-edge at 188 eV
- N K-edge at 401 eV
- TEM mode: $\alpha \approx 0$ mrad; $\beta = 100$ mrad
- Quantification: 47 at.% B / 53 at.% N



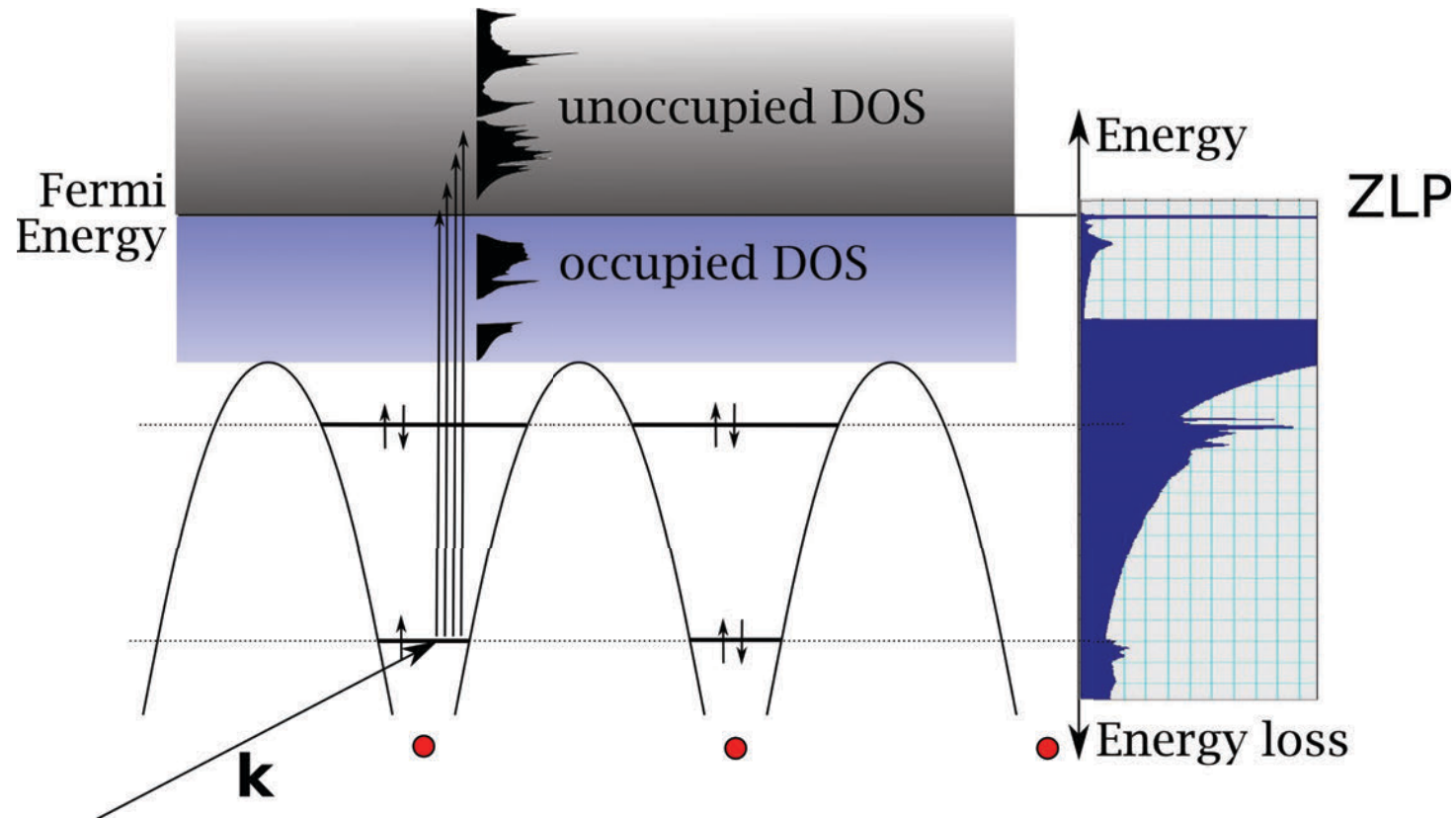
Note: Consider characteristic angle of scattering: $\theta_E \sim \frac{E}{2E_0}$

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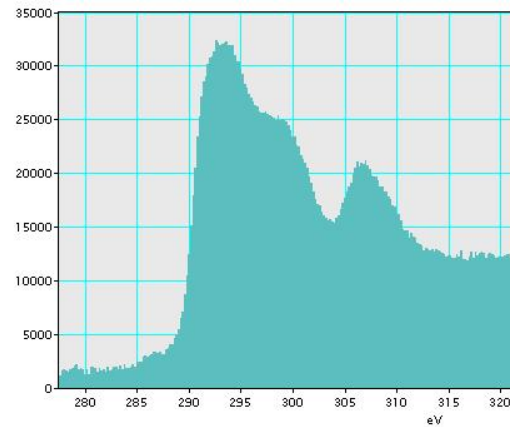
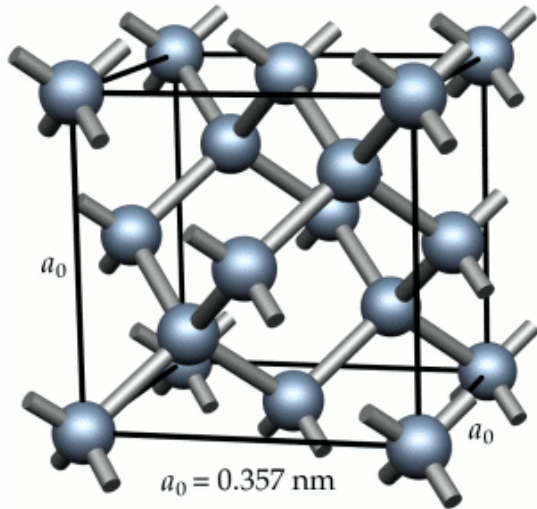
EPFL Energy-loss near edge structure (ELNES)

- Ionisation edge onsets show peaks related to unoccupied density of states (DOS)
- Also called “fine structure”

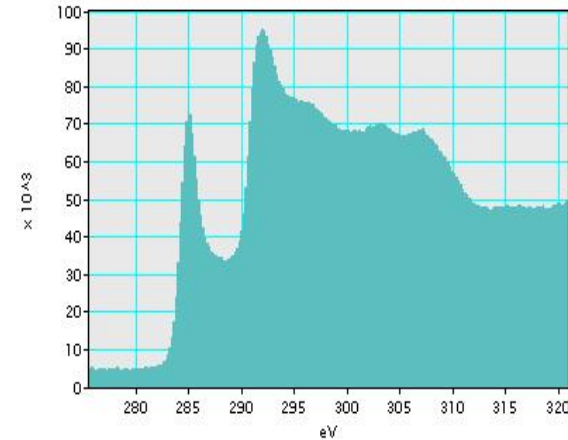
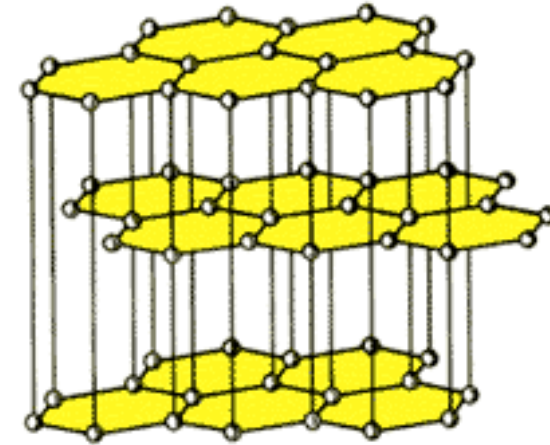


- Example: carbon *K*-edge

Diamond

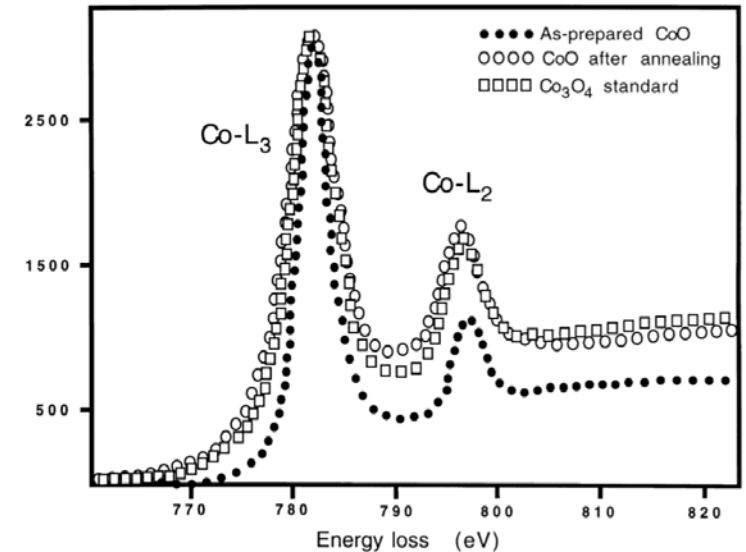
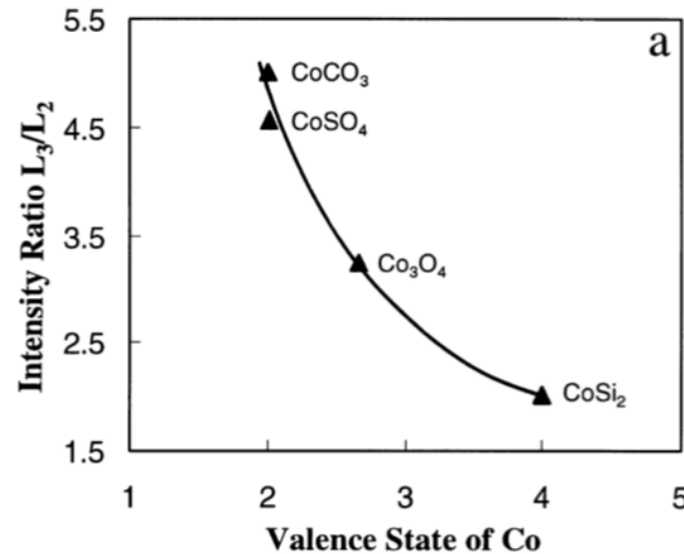
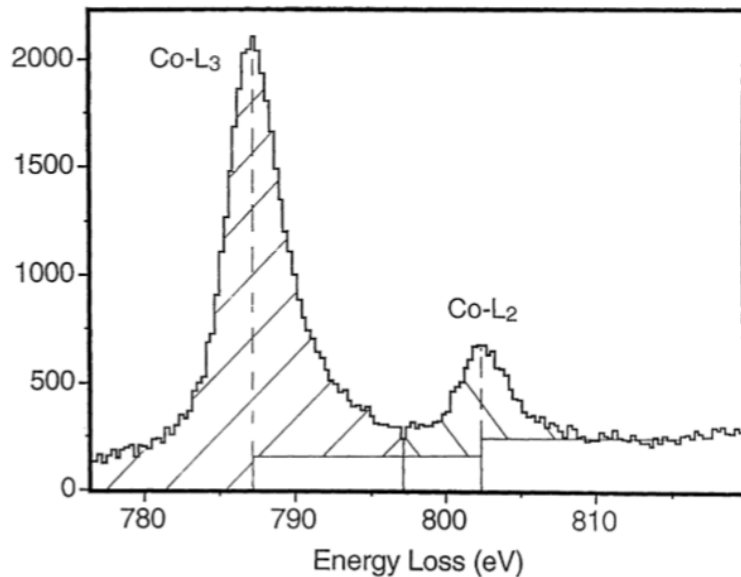


Graphite



EPFL ELNES “White line” analysis

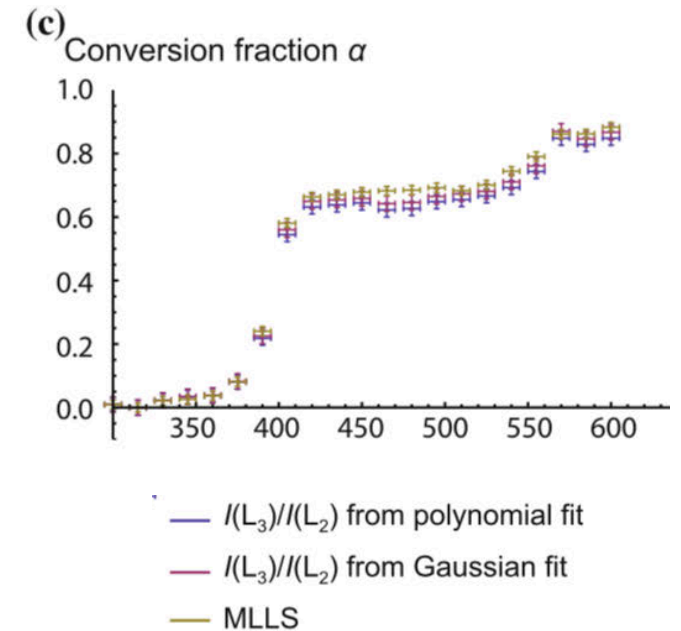
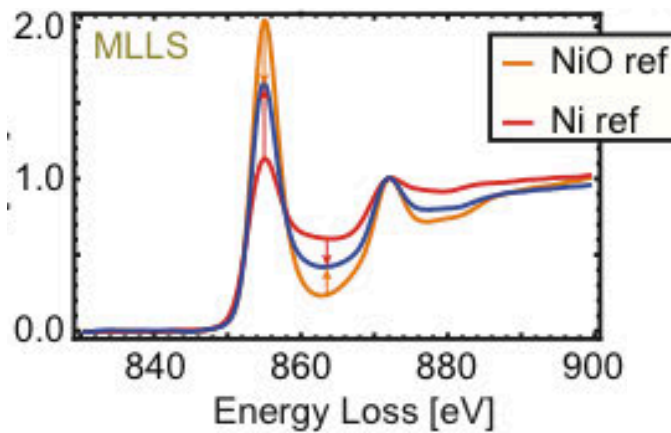
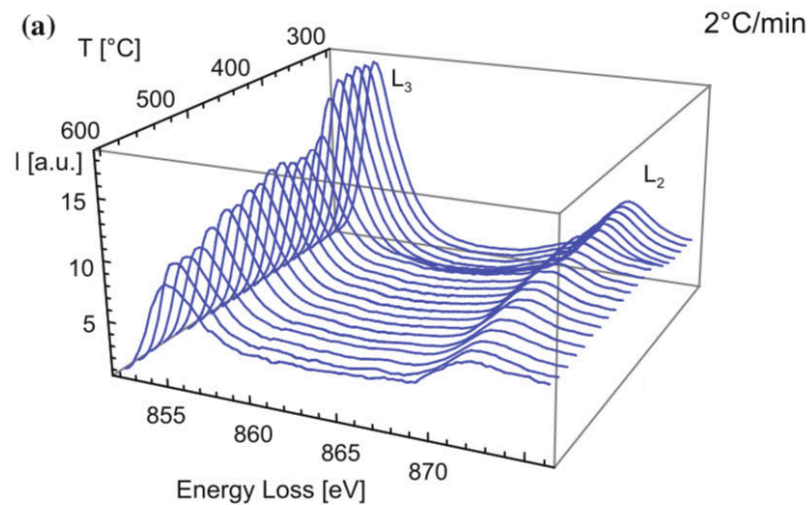
- ELNES peaks used to determine valence/oxidation state e.g. of transition metals
- Example: Co oxidation state



Wang et al. Micron **31** 571 (2000)

EPFL ELNES “White line” analysis

- ELNES peaks used to determine valence/oxidation state e.g. of transition metals
- Example: Ni oxidation state during *in-situ* reduction of NiO



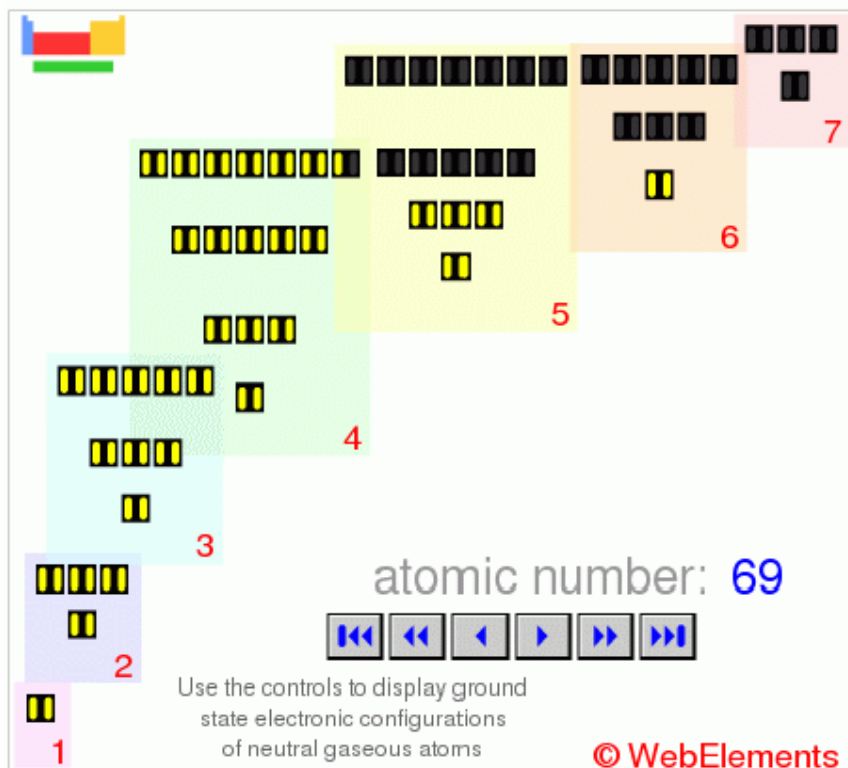
Jeangros et al. J. Mater. Sci. **48** 2893 (2013)

57	68	69	70	71
La	Tm	Yb	Lu	
138.91	168.93	173.04	174.96	
101	102	103	104	105
Md	No	Lr		
(287)	(289)	(262)		

EPFL ELNES fine structure

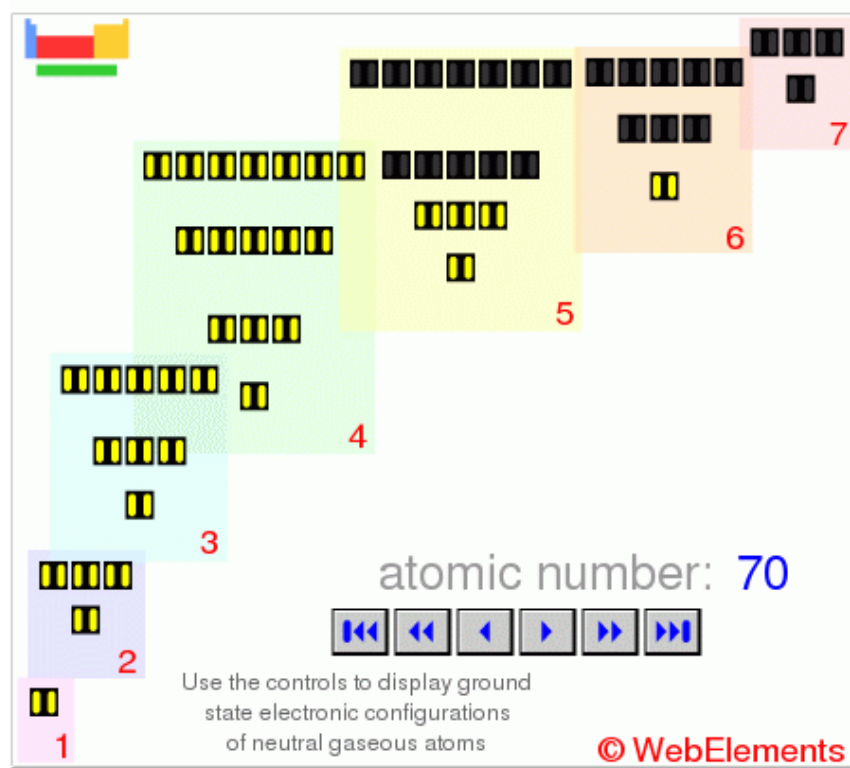
Thulium

- ♦ Ground state electron configuration: $[\text{Xe}].4f^{13}.6s^2$
- ♦ Shell structure: 2,8,18,31,8,2
- ♦ Term symbol: $^2F_{7/2}$

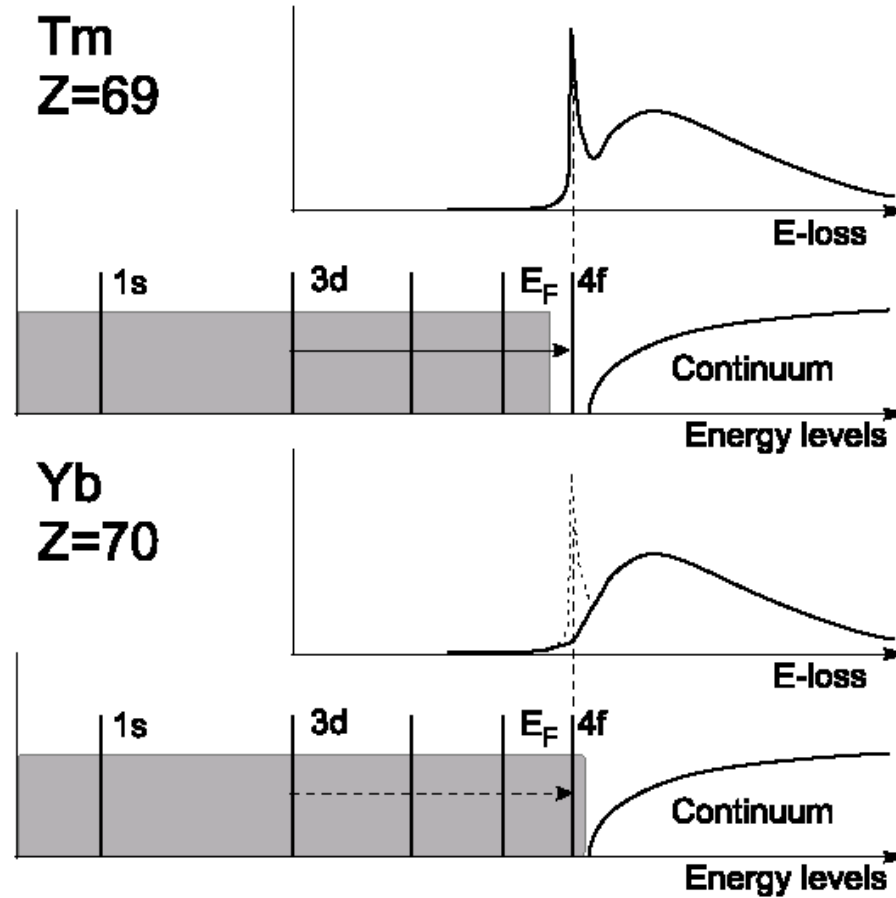


Ytterbium

- ♦ Ground state electron configuration: $[\text{Xe}].4f^{14}.6s^2$
- ♦ Shell structure: 2,8,18,32,8,2
- ♦ Term symbol: 1S_0

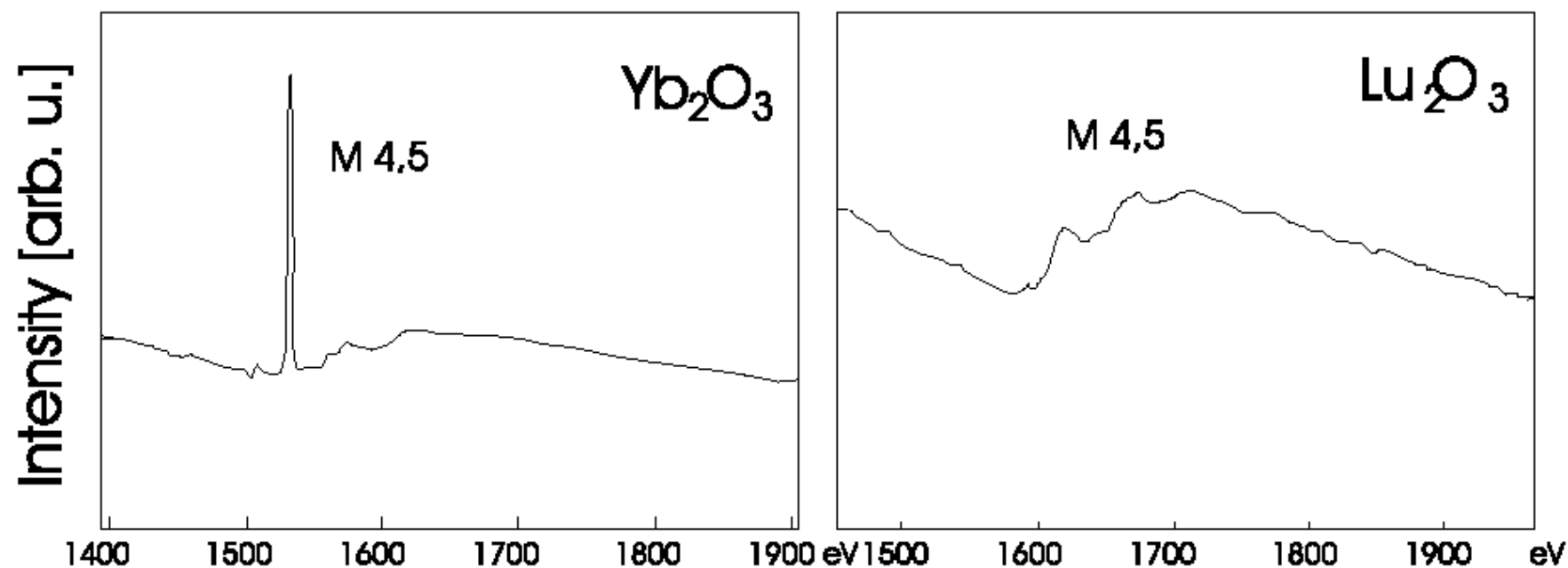


EPFL ELNES fine structure



For Yb ($Z=70$) and higher atomic number, the f-shell is completely filled, and white lines cannot occur.

EPFL ELNES fine structure



M_{45} edges of Yb and Lu in their oxides, showing the disappearance of white line when the f-subshell is filled.